

PAMS Technical Documentation

NHX-7 Transceiver

Chapter 2

Baseband Module JP3

AMENDMENT RECORD SHEET

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System Module JP3: Introduction

This document specifies the System module JP3 of the NHX-7 ETACS cellular phone.

The JP3 System Module comprises the baseband and the RF functions of the phone.

Baseband Sub-module

The Baseband submodule controls the internal operation of the phone. It controls the user interface, i.e. LCD driver, keyboard and audio interface functions. The module performs all signalling towards the system and carries out audio-frequency signal processing. In addition, it controls the operation of the transceiver and stores tuning data for the phone.

The baseband architecture is basically similar to the previous generation. However, the system specified logical voltage level used is 2.82V and new features include a improved charging circuit CHAPS and a new power supply circuit PSA.

The baseband architecture supports a power saving function called "extended standby mode". This sleep mode shuts off the Receiver and part of the NASTA blocks. The phone is woken up at every FOCC:s first word and it is "sleeping" the rest of the time.

The nominal battery voltage in NHX-7 is 3.6V. The actual battery voltage varies between 3.0 to 4.2V/5.3V depending on the used cell type (Li-Ion or NiMH) and whether the phone is connected to a charger (limit on 5.3V with NiMH battery in idle).

Battery charging is controlled by a PWM signal from the MCU. The PWM duty cycle is determined by a charging software. The PWM signal is fed to the CHAPS charging switch and through the charging pins to an external charger. There can be two types of chargers connected to the phone.

Standard chargers (two wires) provide coarse supply power, which is switched by the CHAPS for suitable charging voltage and current.

Advanced chargers (three wires) are equipped with a control input, through which the phone gives PWM charging control signal to the charger.

Block Diagram of baseband

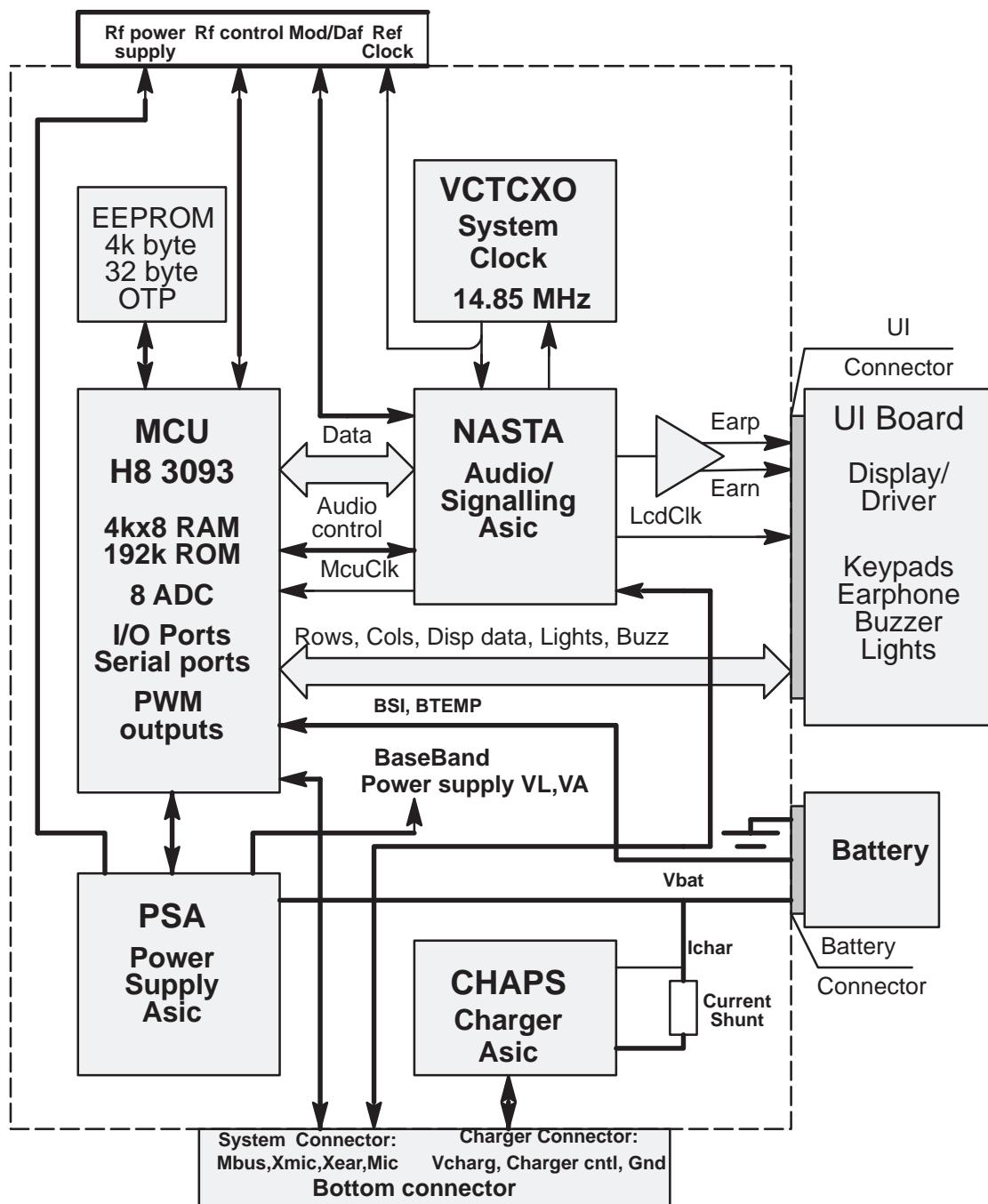


Figure 1.

Technical summary

The baseband module consists of VCTCXO module and four ASIC circuits, PSA, CHAPS, NASTA 4.5, EEPROM, and some standard circuits, DUAL BILATERAL SWITCH (TC7W66F), AUDIO POWER AMPLIFIER (LM4862) and a Hitachi H8 series controller (H8/3093 MCU).

The MCU includes memories, 192 kbytes ROM and 4 kbytes RAM. It controls all transceiver functions.

The EEPROM type is 4 kbytes with 32 bytes. The OTP memory is a serial I²C–bus type.

The baseband is running from a 2.8 V power rail, which is supplied by a power controlling asic. In the PSA asic there are two separate power supplies for BaseBand (VA,VL) and two externally controllable power supplies for RF (VRX, VTX).

The CHAPS is a charging control ASIC. It is essentially an integrated power switch for controlling charging current, in a mobile phone. CHAPS is designed for 3 cell Nickel or 1 cell Lithium battery packs.

The NASTA circuit integrates the Audio and Modem operations. Because the NASTA supports only one microphone, there are two bilateral switches to connect the internal microphone or the headset microphone to the NASTA MIC input. There is an audio power amplifier for EAR and XEAR lines each. The internal earphone amplifier is a dual ended type output which is in EAR line and there is transistor buffer in XEAR line.

The VCTCXO module is a voltage and temperature controlled oscillator which operates as system clock for RF and BaseBand.

All functional blocks of the baseband are mounted on a single multi layer printed circuit board. All components of the baseband are surface mountable. This board contains also the RF-parts. The B-cover side (battery side) EMC shielding is implemented by using a metallic RF-shields on the RF-blocks. On the other side the engine is shielded with a aluminium frame, which makes a contact to a ground ring of the engine board and a ground plane of the UI-board.

The connections from BaseBand to UI board are fed through a 28-way 2–row board to board spring connector.

Modes of Operation

Power off, Standby, Listening and Conversation modes.

- In Power off mode only the circuits needed for power up are supplied.
- In Standby mode the MCU and needed blocks of the NASTA are active.
- In Listening mode the receiver and some blocks of the NASTA are active.
- In Conversation mode all ICs are active.

CTRLU Circuit

The Control block CTRLU controls all functions of the phone.

Block Description

– CTRLU – PWRU

CTRLU controls the watchdog timer in PSA. It sends a negative pulse at approximately 0,1 s to XPWROFF pin of the PSA to keep the power on. If CTRLU fails to deliver this pulse, the PSA will remove power from the system. When power off is requested CTRLU leaves PSA watchdog without reset. After the watchdog has elapsed PSA cuts off the supply voltages from the phone. CTRLU controls also the charger on/off switching in the PWRU block. Battery charging is controlled by CSW line, which is PWM-controlled output port.

– CTRLU – AUDIO

Interface between microcontroller and the NASTA circuit is bidirectional 8-bit data bus with 4 address lines. Address, data and control lines are used in microcontroller as I/O-port pins. Data lines direction must be controlled with microcontroller data direction register. Interface includes address outputs NA0–3, data inputs (read) / outputs (write) ND0–7, chip select control output XNCS , read control output XNRD, write control output XNWR and interrupt input XINT. To minimize power consumption, control signals XRD and XCS should be in '0' state and address output NA0–3 and NWR in '1' state and data lines ND0–7 should be inputs .Buzzer is controlled by BUZZ_DRV PWM signal. Headset adapter is detected by HSCONN input.

– CTRLU – UIF and DISPLAY

Keyboard is connected directly to the controller. COL 0:3 are output lines and ROW 0:3 are input lines. Watchdog is updated same time with keyboard scanning (XPWROFF). Keyboard scanning is done by driving one COL to 0 V at time and ROWs are used to read which key is pressed.

Keyboards lights are controlled by KEYBLIGHT signal and LCD lights by LCDBLIGHT signal.

LCD controller interface to microcontroller is a bidirectional data line LCDDA, data serial clock line SCLK output, chip select control LCDENX output, command or display data control LCDCC output and reset control LCDRES output.

– CTRLU – RECEIVER

Received signal strength is measured over the RSSI line and intermediate frequency is measured over the IF line.

RX synthesizer and receiver are powered on/off by PSBS_EN line.

– CTRLU – SYNTHESIZER

Frequency is controlled by the AFC signal. The synthesizer is controlled via the synchronous serial bus SDAT/SCLK. The data is latched to the synthesizer by the positive edge of the SLE line. The TX synthesizers power on/off is controlled by VTX_ENA signal.

– CTRLU – TRANSMITTER

The transmitter on/off state is detected over the TXI line. The TXE line activates the power module. The power is controlled via the TXC line which is a PWM-controlled output port (frequency about 9.4 kHz).

Extended standby mode for power saving

The extended standby mode is automatically activated when the phone is working in the control channel (FOCC). The NASTA runs this function, switching on/off the receiver's power supply.

PSPS_EN signal:

- The signal connects the RX regulator on via the PSA when it is in "1" state, in "0" state the RX regulator is off.

HPD_EN signal:

- The signal controls the RX synthesizers hardware power down function.

When it is in "1" state the RX synthesizer is powered up, in "0" state the RX synthesizer is powered down.

Main Components

MCU

The H8/3093 is a CMOS microcontroller. All the memory needed (192kB ROM, 4kB RAM) except the EEPROM, is located in the controller. The MCU operating clock (2.4 MHz) is generated on the NASTA and the VCTCXO. The H8/3093 is operating in single-chip normal mode (mode 3) 192kbyte address space, so all input/output pins are used as I/O-ports.

Pin Number	Port	Signal	Description
1	PB0	SDAT	Synthesizer data line
2	PB1	RSSI_READY	RSSI readings synchronization
3	PB2	VIBRA_CONTROL	Vibra alerting device on/off
4	PB3	RXD	M2BUS net free timer input
5	PB4	EAREN	Earphone amplifier enable
6	PB5	XPWROFF	Power off control
7	PB6	PWRON	Power button state
8	PB7	SLE	Synthesizer latch enable
9	P90	TXD	Serial interface (M2BUS)

Pin Number	Port	Signal	Description
10	P92	RXD	Serial interface (M2BUS)
11	P94	ECLK	Serial data clock for EEPROM
12	VSS	GND	
13 – 20	P30 – P37	ND0 – ND7	Parallel data bus for NASTA
21	VCC	VL	
22	P10	NA0	Address line for NASTA
23	P11	NA1	Address line for NASTA
24	P12	NA2	Address line for NASTA
25	P13	NA3	Address line for NASTA
26	P14	XNCS	NASTA chip select
27	P15	XNWR	Write control to NASTA
28	P16	XNRD	Read control to NASTA
29	P17	LIGHTS	Keypad backlight control
30	VSS	GND	
31 – 34	P20 – P23	COL0–COL3	Keypad outputs
35 – 38	P24 – P27	ROW0 – ROW3	Keypad inputs (Input pullup used)
39	P50	SCLK	Serial data clock for lcd driver
40	P51	LCDENX	Chip select signal for lcd driver
41	P52	LCDCC	Display or Command data
42	P53	LCDSDA	Data line for lcd driver
43	P60	VTX_ENA	TX synthesizer enable. Active high
44 – 45	MD0 – MD1		Mode selection
46	NC	NC	
47	STBY	VL	
48	RES	XRES	Reset from PSA
49	NMI	NC	
50	VSS	GND	
51	EXTAL	CLKMCU	External system clock from NASTA
52	XTAL	NC	
53	VCC	VL	
54	P63	TXE	Transmitter on/off
55	P64	LIM	Battery cut off limit selection

Pin Number	Port	Signal	Description
56	P65	XEAR_EN	Headset earpiece amplifier control
57	RESO	NC	
58	AVSS	GND	
59	P70	VBATSW	Battery voltage
60	P71	VCHARG	Charger voltage
61	P72	ICHAR	Charging current measurement
62	P73	BTEMP	Battery temperature
63	P74	RSSI	Received signal strength
64	P75	TXI	Transmitter state monitor
65	P76	HSCON	Headset detecting voltage
66	P77	BSI	Battery size indicator
67	VREF	VA	
68	AVCC	VA	
69	P80	XINT	Interrupt request from NASTA
70	P81	LCDRES	LCD reset signal
71	P82	LCDBLIGHT	LCD backlight control
72	P83	HEADSW	Headset switch indicator
73	PA0	MIC_EN	Internal microphone control
74	PA1	LCDCLK	LCD clock from NASTA
75	PA2	BUZZ_DRV	PWM output for buzzer
76	PA3	SCLK	Serial clock for synthesizer
77	PA4	CSW	Charging control PWM
78	PA5	EDATA	Eeprom data line
79	PA6	TXC	Transmitter power control
80	PA7	XMIC_EN	Headset microphone control

EEPROM

There is one 4kbyte EEPROM with 32byte OTP memory in the phone. The EEPROM is a nonvolatile memory in which the tuning data for the phone is stored. In addition, it contains the short code memory locations to retain user selectable phone numbers. The OTP memory is ROM area for identification and security purposes.

Table 1. EEPROM signals:

Pin No	Signal	Description
5	SDA	I ² C bus data
6	SCL	I ² C bus clock

PWRU Circuit

Power Distribution

The main components of the Power Unit are the PSA (Power Supply Asic) and the CHAPS (Charger Power Switch).

In normal operation the baseband is powered from the phone's battery. The battery consists of three Nickel Metal Hydride cells. There is also a possibility to use batteries consisting of one Lithium-Ion cell. An external charger is used for recharging the battery and supplying power to the phone. The charger can be either a standard charger that can deliver around 400 mA or a so called performance charger, which can deliver supply current up to 850 mA.

The baseband contains components that control the power distribution to the whole phone excluding those parts that use continuous battery supply. The battery feeds power directly to three parts of the system: PSA, RF-power amplifier, and UI (buzzer and display and keyboard lights).

The power management circuit CHAPS provides protection against overvoltages, charger failures and pirate chargers etc. that could otherwise cause damage to the phone.

Table 2. DC Characteristics of PWRU signals

Signal name	From To	Parameter	Minim-um	Typi-cal	Maxi-mum	Unit	Function
VBATT	Battery RF/UIF	Voltage	3.0	3.6	5.0/5.3	V	Supply voltage for RF and UIF
		Current			3500	mA	
XRES	PSA MCU,NAS- TA,UIF	Logic high "1"	0.7*VL		VL	V	PSA is Power On Mode
		Logic low "0"	0		0.3*VL	V	PSA is Power Off or Reset Mode

Table 2. DC Characteristics of PWRU signals (continued)

Signal name	From To	Parameter	Min- imum	Typi- cal	Maxi- mum	Unit	Function
LIM	MCU CHAPS	Logic high "1"	VL–0.5		VL	V	Cutoff limit 5.0 V
		Logic low "0"	0		0.4	V	Cutoff limit 4.6 V
XPWRON	UIF PSA	Logic high "1"	0.7* VBAT		VBAT	V	Power On switch open
		Logic low "0"	0		1.2	V	Power On switch closed
XPWR OFF	MCU PSA	Logic high "1"	VL–0.5		VL	V	Watchdog counter not reset
		Logic low "0"	0		0.4	V	Watchdog counter re-set "1" → "0"
PWRON	PSA MCU	Logic high "1"	0.7*VL		VL	V	PSA is in Power On Mode
		Logic low "0"	0		0.3*VL	V	PSA is in Power Off or Reset mode
PSBS_EN (Phone Supported Battery Save)	NASTA PSA	Logic high "1"	2.0		2.90	V	VRX Enabled
		Logic low "0"	0		0.5	V	VRX Disabled
HPD_EN	NASTA PLL circuit	Logic high "1"	2.0		2.90	V	Hardware power down disabled on PLL circuit
		Logic low "0"	0		0.4	V	Hardware power down enabled on PLL circuit
VTX_ENA	MCU PSA	Logic high "1"	VL–0.5		VL	V	TX VCO and synthesizer powered on
		Logic low "0"	0		0.4	V	TX VCO and synthesizer powered off
VBATSW	PSA MCU	Voltage	0		2.45	V	Switched internally divided VBAT voltage
		VBATSW/VBAT division ratio	0.436	0.45	0.464		
VCHARG	PSA MCU	Voltage	0		2.8	V	Switched Charger voltage
		VCHRSH switch resistance	0	0.25	1.0	Kohm	
ICHR	AMPLIFI-ER MCU	Voltage	0		2.90	V	Charger Current Measurement over the shunt resistor.
TXD	MCU PSA	Logic high "1"	VL–0.5		VL	V	M2BUS data output, PSA M2BUS output is in high-Z state.
		Logic low "0"	0		0.4	V	M2BUS data output, PSA M2BUS output is LOW

Table 2. DC Characteristics of PWRU signals (continued)

Signal name	From To	Parameter	Min- imum	Typi- cal	Maxi- mum	Unit	Function
RXD	PSA MCU	Logic high "1"	2.0		2.90	V	M2BUS data input
		Logic low "0"	0		0.5	V	
CSW	MCU PSA	Logic high "1"	2.0		2.90	V	Charger switch and ACP-9 control signal
		Logic low "0"	0		0.5	V	
		PWM frequency	1		32	Hz	
		PWM duty cycle	0		100	%	

Battery charging

Acceptable chargers are detected by the software. The absolute maximum input voltage is 30V due to the transient suppressor that is protecting the charger input. At the phone end there is no difference between a plug-in charger or a desktop charger. The DC-jack pins and bottom connector charging pads are connected together inside the phone. The charging block diagram is below.

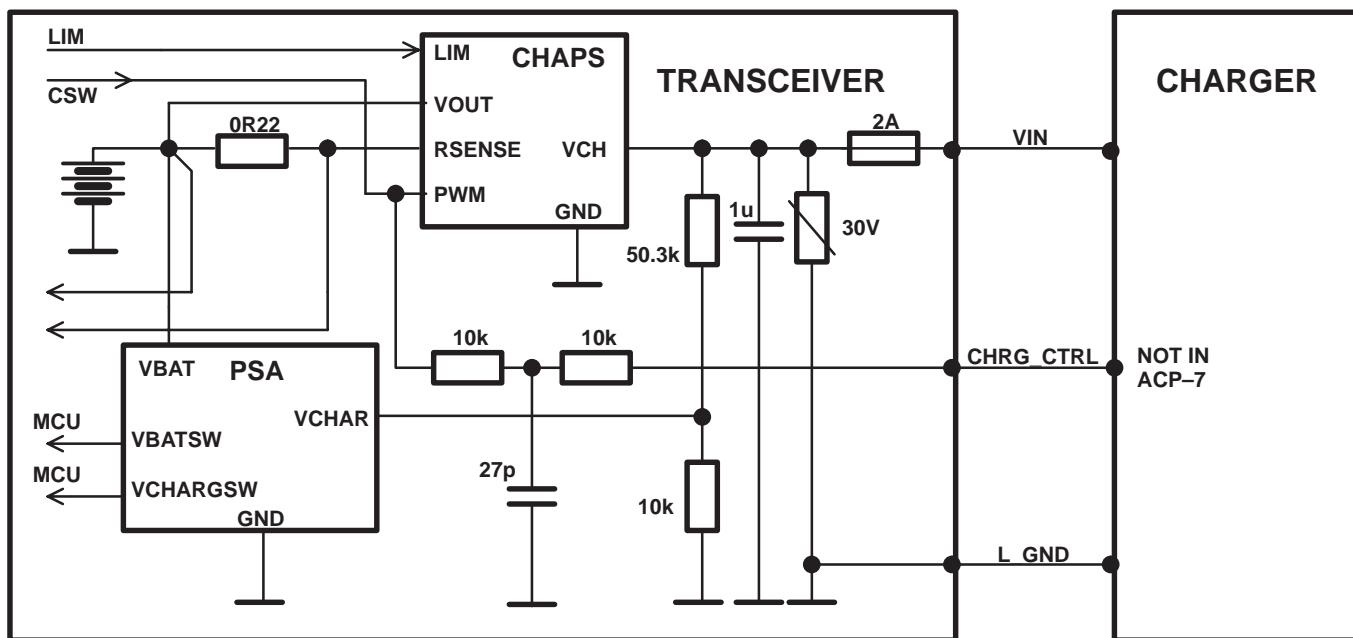


Figure 2. Charging block diagram

Startup charging

When a charger is connected, the CHAPS is supplying a startup current minimum of 130mA to the phone. The startup current provides initial

charging to a phone with an empty battery. The startup circuit charges the battery until the battery voltage level reaches 3.0V (+/- 0.1V) and the PSA releases the PURX reset signal and program execution starts. Charging mode is changed from startup charging to PWM charging that is controlled by the MCU software. If the battery voltage reaches 3.55V (3.75V maximum) before the program has taken control over the charging, the startup current is switched off. The startup current is switched on again when the battery voltage has decreased to 100mV (nominal).

Table 3. Startup characteristics

Parameter	Symbol	Min	Typ	Max	Unit
VOUT Start- up mode cutoff limit	Vstart	3.45	3.55	3.75	V
VOUT Start- up mode hysteresis NOTE: Cout = 4.7 uF	Vstarthys	80	100	200	mV
Start-up regulator output current VOUT = 0V ... Vstart	Istart	130	165	200	mA

Battery overvoltage protection

Output overvoltage protection is used to protect phone from damage. This function is also used to define the protection cutoff voltage for different battery types (Li or Ni). The power switch is immediately turned OFF if the voltage in VOUT rises above the selected limit VLIM1 or VLIM2.

Table 4. VLIM characteristics

Parameter	Symbol	LIM input	Min	Typ	Max	Unit
Output voltage cutoff limit (during transmission or Li-battery)	VLIM1	LOW	4.4	4.6	4.8	V
Output voltage cutoff limit (no transmission or Ni-battery)	VLIM2	HIGH	4.8	5.0	5.2	V

The voltage limit (VLIM1 or VLIM2) is selected by logic LOW or logic HIGH on the CHAPS (N101) LIM- input pin. Default value is lower limit VLIM1.

When the switch in output overvoltage situation has once turned OFF, it stays OFF until the the battery voltage falls below VLIM1 (or VLIM2) and PWM = LOW is detected. The switch can be turned on again by setting PWM = HIGH.

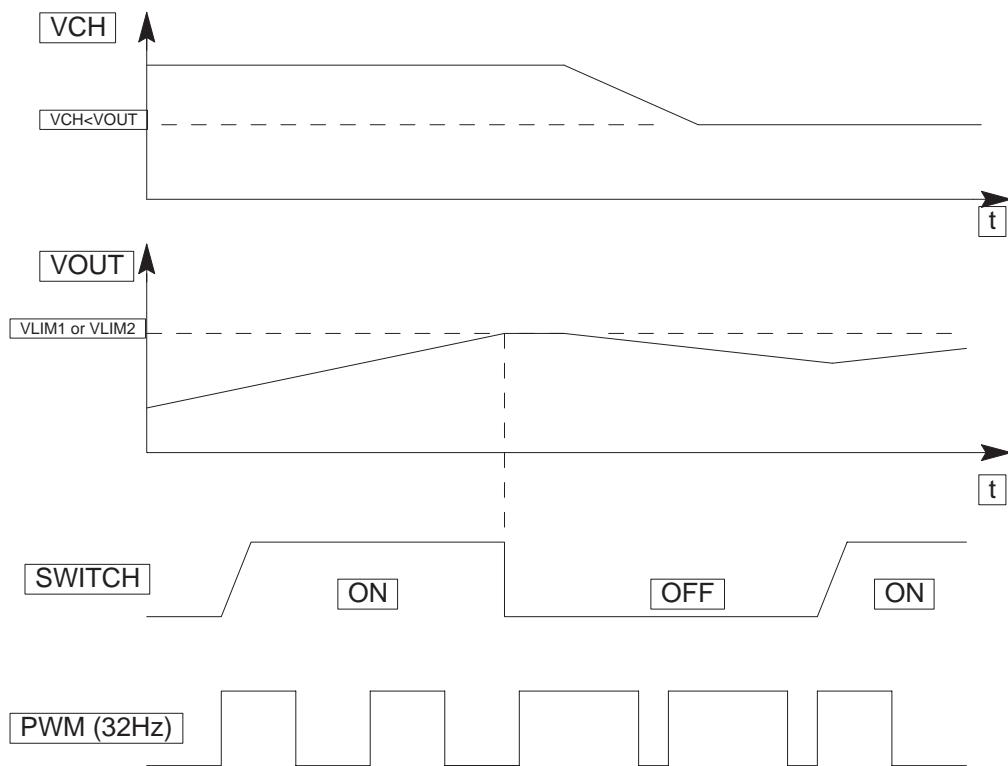
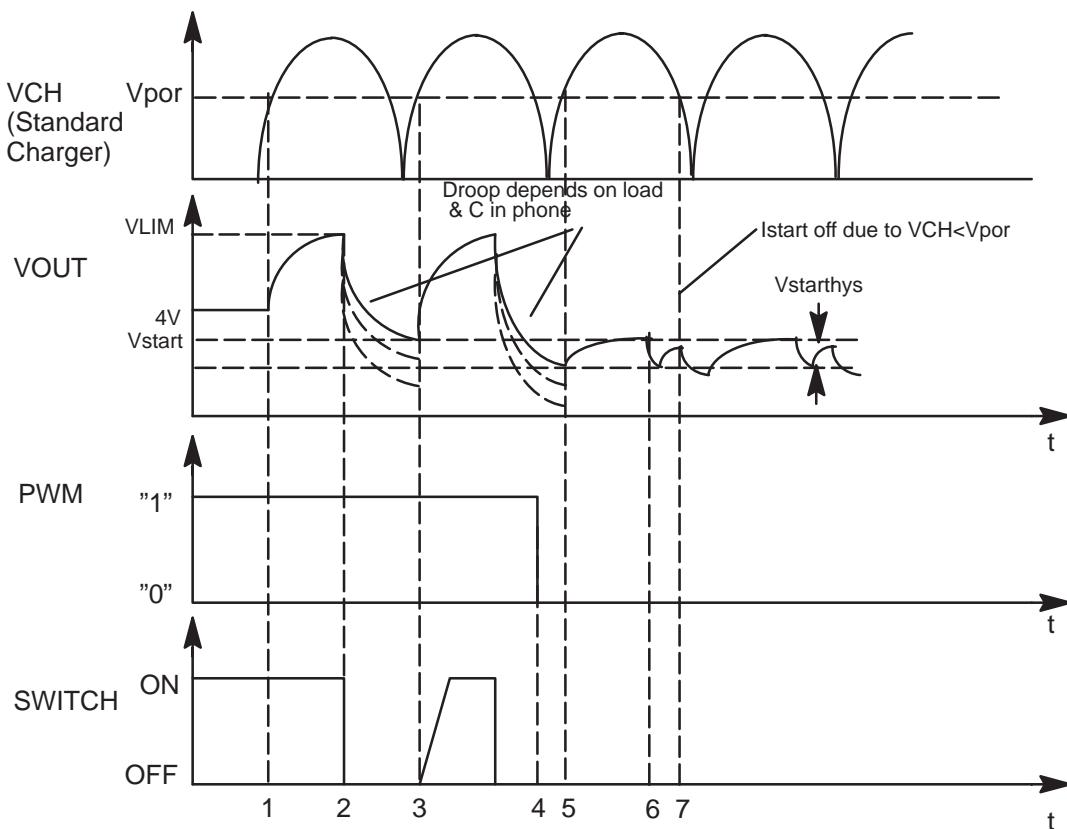


Figure above: Battery overvoltage protection

Battery removal during charging

Output overvoltage protection is also needed in case the main battery is removed when a charger connected or a charger is connected before the battery is connected to the phone.

With a charger connected, if **VOUT** exceeds **VLIM1** (or **VLIM2**), the CHAPS turns switch OFF until the charger input has decreased below **Vpor** (nominal 3.0V, maximum 3.4V). The MCU software stops the charging (turn off PWM) when it detects that the battery has been removed. The CHAPS remains in protection state as long as the PWM stays HIGH after the output overvoltage situation has occurred.



1. Battery removed, (standard) charger connected, V_{OUT} rises (follows charger voltage)
2. V_{OUT} exceeds limit $VLIM(X)$, switch is turned immediately OFF
3. V_{OUT} falls (because no battery), also $V_{CH} < V_{por}$ (standard chargers full-rectified output). When $V_{CH} > V_{por}$ and $V_{OUT} < VLIM(X)$ \rightarrow switch turned on again (also PWM is still HIGH) and V_{OUT} again exceeds $VLIM(X)$.
4. Software sets PWM = LOW \rightarrow CHAPS does not enter PWM mode
5. PWM low \rightarrow Startup mode, startup current flows until V_{start} limit reached
6. V_{OUT} exceeds limit V_{start} , I_{start} is turned off
7. V_{CH} falls below V_{por}

Figure above: Battery removal during charging

Different PWM frequencies (2Hz and 32 Hz)

When a travel charger (2-wire charger) is used, the power switch is turned ON and OFF by the PWM input when the PWM rate is 2Hz. When the PWM is HIGH, the switch is ON and the output current I_{out} = charger current - CHAPS supply current. When PWM is LOW, the switch is OFF and the output current I_{out} = 0. To prevent the switching transients inducing noise in audio circuitry of the phone soft switching is used.

The performance travel charger (3-wire charger) is controlled with PWM at a frequency of 32Hz. When the PWM rate is 32Hz CHAPS keeps the power switch continuously in the ON state.

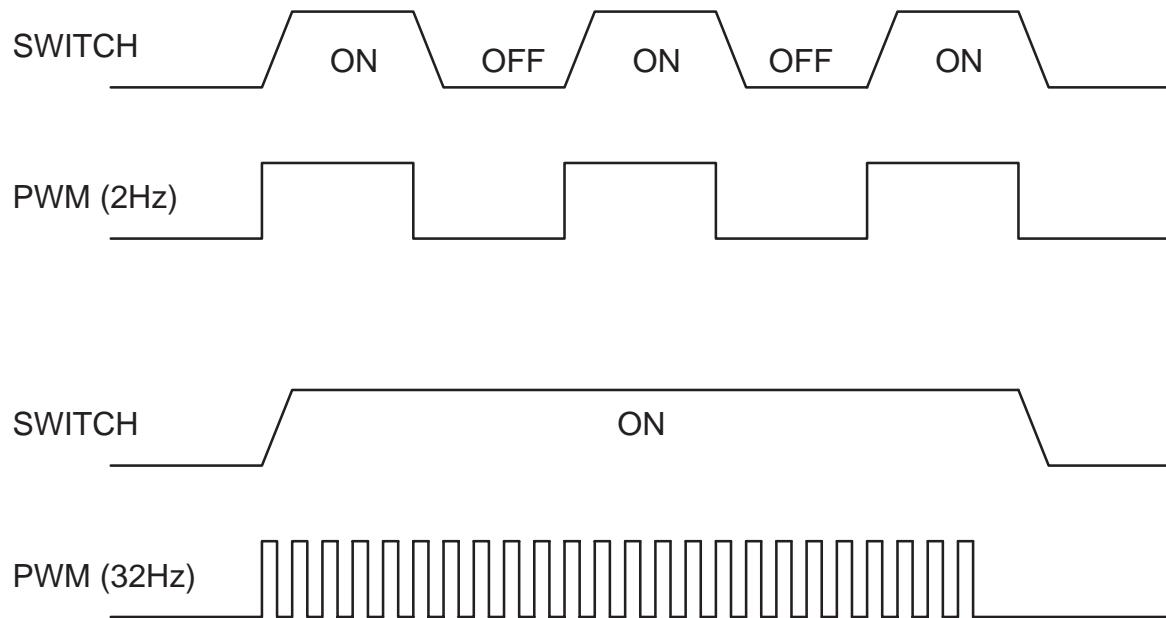


Figure 3. Switch control with 2Hz and 32 Hz frequencies (in this case 50% duty cycle)

Charger Current measurement

The charging current measurement is based on the reading of differential voltages over the shunt resistor at the CHAPS output lines. The voltage is measured and amplified by a differential amplifier and it is carried to the MCU A/D converter. Measurement area is up to 1400 mA and 1 A/D bit equals 1.85 mA. The charging current calibration is done with 0 mA and 500 mA in production test line. When charger is connected the current measurement connection is activated. The A/D-conversion result and charging current can be calculated from equations :

$$\text{A/D readout} = 1024 * V_{\text{ICCHAR}} / V_{\text{REF}}$$

Charging current:

$$I = (V_{\text{ICCHAR}} - V_{\text{ICCHAR}}(0\text{mA})) * (500\text{mA}/(V_{\text{ICCHAR}}(500\text{mA}) - V_{\text{ICCHAR}}(0\text{mA}))$$

where $V_{\text{REF}}=2.82 \text{ V}$

V_{ICCHAR} = voltage in ICHAR line

Table 5. Charger current measurement

Name	Min	Typ	Max	Unit	Notes
V_{ICHAR}	0.46	0.69	0.92	V	Charging current is 0 mA. (Calibration point)
	163	250	334	A/D	
	1.22	1.44	1.65	V	Charging current is 500 mA. (Calibration point)
	443	522	598	A/D	
	1.98	2.19	2.39	V	Charging current is 1000 mA.
	718	795	867	A/D	

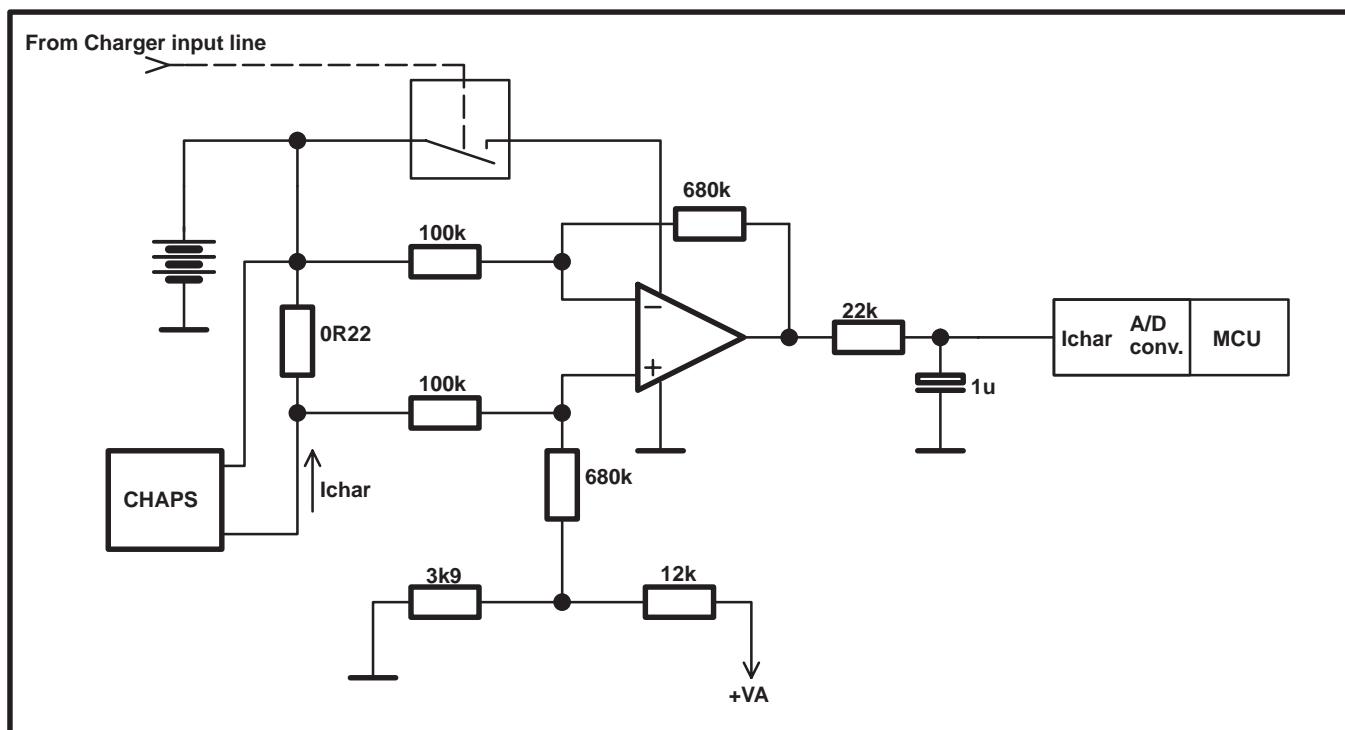


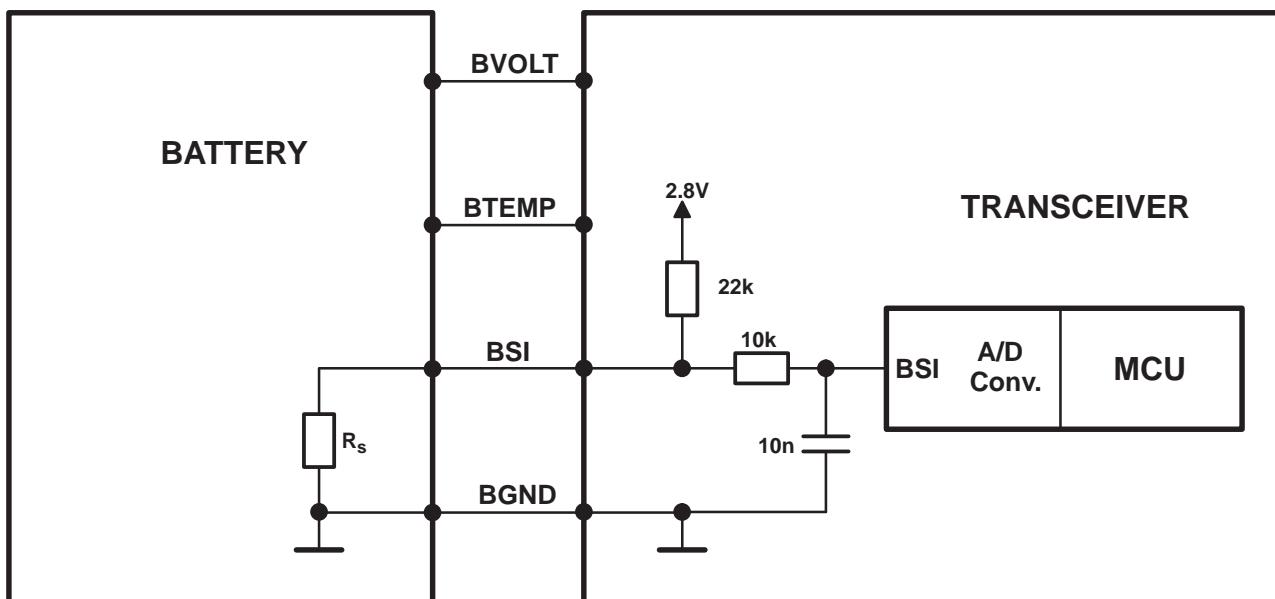
Figure 4. Charger current measurement

Battery identification

Different battery types are identified by a pull-down resistor inside the battery pack. The BSI line inside transceiver has a 22k pull-up to VA. The MCU can identify a battery by reading the BSI line DC-voltage level with a MCU (D201) A/D-converter.

Table 6. Battery Identification

Name	Min	Typ	Max	Unit	Notes
BSI	0		2.8	V	Battery size indication 22k pullup resistor to VA in phone
	14.2	15	15.8	kohm	Indication of a BMS-2V vibra battery (900mAh NiMH)
	9.5	10	10.5	kohm	Indication of a BMS-2S battery (900mAh NiMH)
	37	39	41	kohm	Indication of a BLS-2 battery (900mAh Lilon)
	48.5	51	53.5	kohm	Indication of a BLS-4 battery (1600mAh Lilon)
	-5		5	%	Indication resistor and pullup resistor tolerance

**Battery voltage measurement, VBATSW**

Battery voltage can be measured up to 6.27 V from the VBATSW line. The absolute accuracy is low because of the voltage reference and A/D-converter \pm 8 LSB accuracy . This battery voltage measurement offset error must be calibrated with input voltage 4.1 V. The A/D conversion result can be calculated from equation:

$$\text{A/D readout} = 1024 * (\text{VBAT} * (0.45)) / \text{VREF} \quad \text{VREF}=2.82 \text{ V}$$

For example:

4.1 V	results	670 = 29Dh
3.6 V	results	588 = 24Ch
3.0 V	results	490 = 1EAh

Charger voltage measurement, VCHARG

Charger voltage can be measured up to 17.00 V from VCHARG line. The absolute accuracy is low because of the voltage reference and A/D-con-

verter ± 8 LSB accuracy. The A/D-conversion result can be calculated from equation :

$$\text{A/D readout} = 1024 * (\text{VCHARG} * (10/60.3)) / \text{VREF} \quad \text{VREF}=2.82 \text{ V}$$

For example:

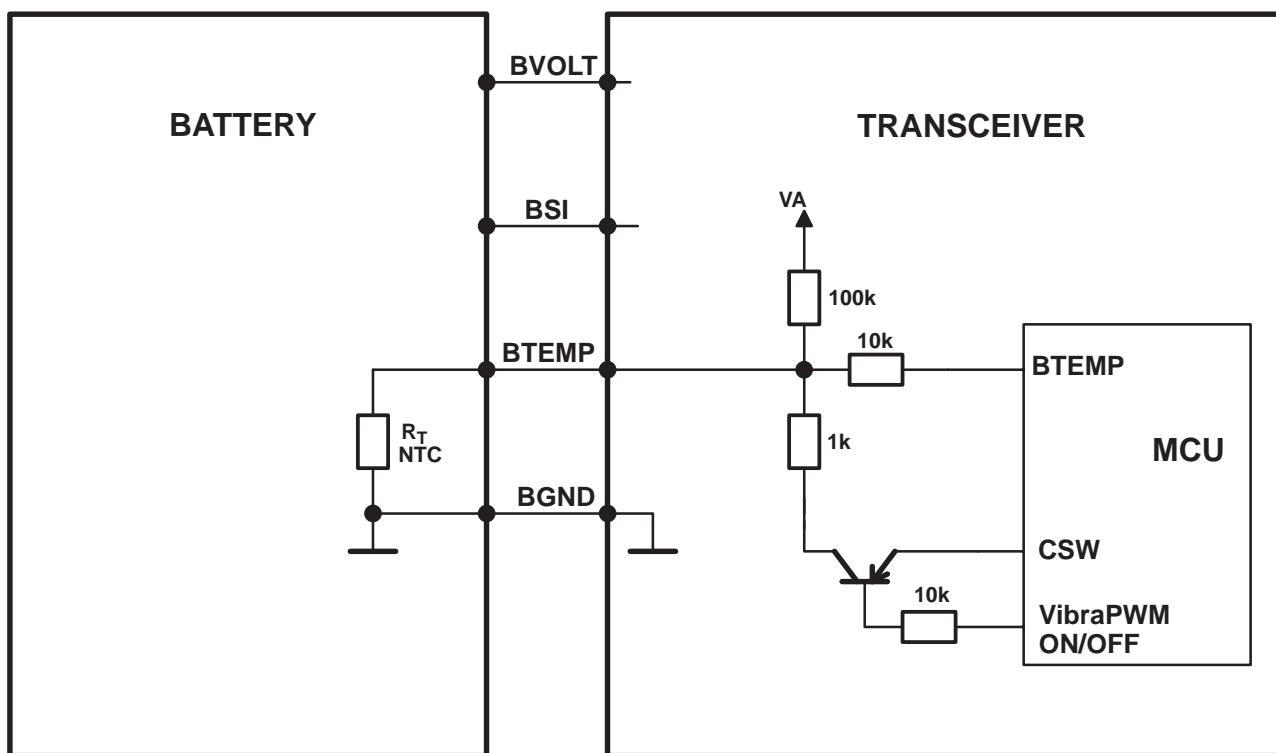
$$8.4 \text{ V} \quad \text{results} \quad 506 = 1F9h$$

Battery temperature

The battery temperature is measured with a NTC inside the battery pack. The BTEMP line inside transceiver has a 100k pullup to VA. The MCU can calculate the battery temperature by reading the BTEMP line DC-voltage level with a MCU (D201) A/D-converter.

Table 7. Battery temperature

Pin	Name	Min	Typ	Max	Unit	Notes
3	BTEMP	0		2.90	V	Battery temperature indication 100k pullup resistor to VA in phone Battery package has NTC pull down resistor: $47k \pm 5\% @ +25C$, $B=4050 \pm 3\%$
		-1		1	%	100k pullup resistor tolerance



Battery temperature monitoring schematic diagram above

Based on $47k\Omega \pm 5\%$ NTC with $B = 4090 \pm 1.5\%$. Without any alignment, with that and 1 % pull-up resistor, $\pm 2.5^\circ\text{C}$ accuracy is achieved between -20 and $+60^\circ\text{C}$ ($\pm 3.5^\circ\text{C}$ @ $-40 \dots +85^\circ\text{C}$).

Table 8. Battery temperature vs. AD readings and NTC resistance

T [°C]	AD	R [kΩ]	T [°C]	AD	R [kΩ]	T [°C]	AD	R [kΩ]
-40	963	1589	5	560	120.9	50	145	16.53
-35	942	1151	10	497	94.53	55	122	13.63
-30	915	842.8	15	436	74.40	60	103	11.30
-25	882	622.6	20	379	58.95	65	88	9.404
-20	842	464.1	25	327	47.00	70	74	7.865
-15	795	349.0	30	280	37.71	75	63	6.607
-10	743	264.6	35	238	30.43	80	54	5.573
-5	685	202.3	40	202	24.70	85	46	4.721
0	623	155.8	45	171	20.15	90	39	4.015

Vibra alerting device

A vibra alerting device is used for giving silent signal to the user of an incoming call. The device is not placed in the phone but it will be added to a special battery pack. The vibra is controlled with a PWM signal by the MCU via the BTEMP battery terminal.

Table 9. Vibra battery connection

Name	Min	Typ	Max	Unit	Notes
BTEMP	9	11	14	kHz	PWM control to VIBRA BATTERY
BSI	0		2.90	V	Battery size indication Phone has 100kohm pull up resistor.
	14.2	15	15.8	kohm	Battery size indication resistor (vibra battery)

A 15kohm BSI resistor is needed to detect the vibra battery. It is only used to enable vibra selection in user menu. When alerting, VibraPWM signal is delivered to battery.

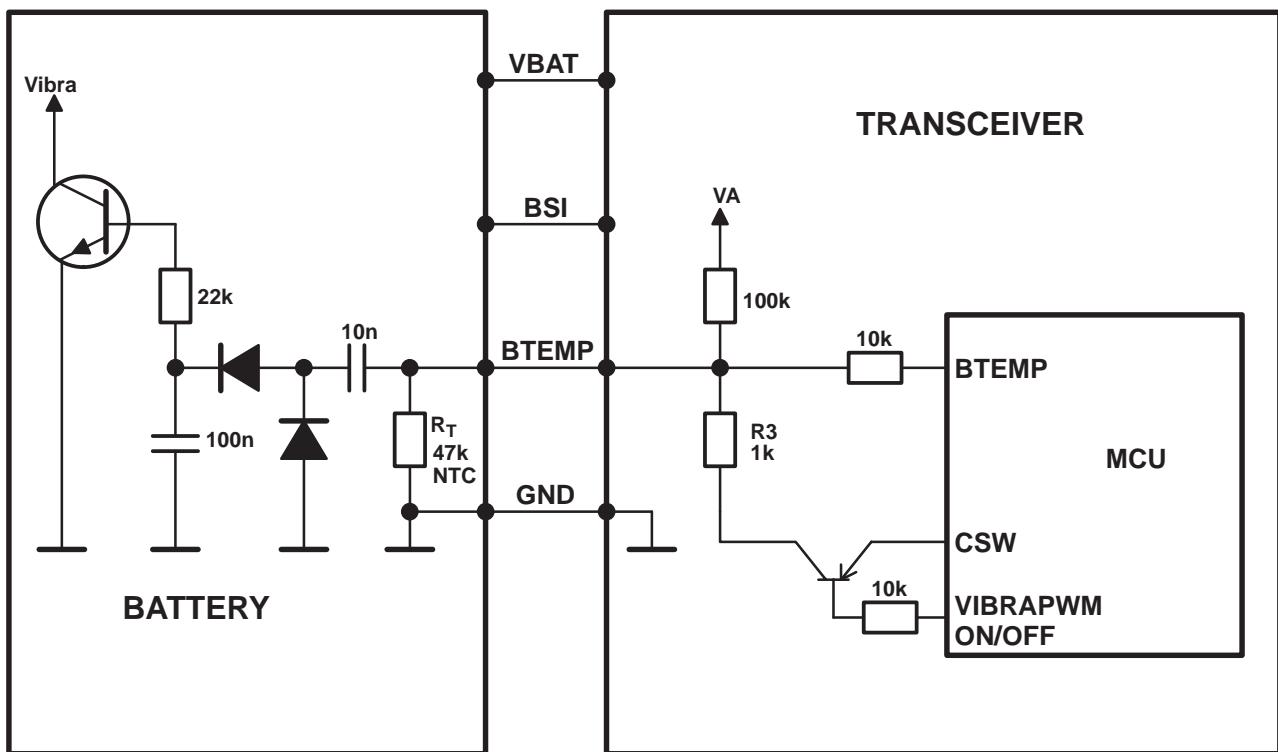


Figure 5. Vibra battery

Supply voltage regulators and controlling

The heart of the power distribution is the PSA asic. It includes all the voltage regulators and feeds power to the whole system. The baseband digital and analog parts are powered from the VL and VA regulators which provide the 2.82 V baseband supply. The baseband regulators are active when the phone is powered on.

The PSA includes also two 2.82 V regulators (VRX and VTX) providing power to the RF section. These regulators can be controlled by the direct control signals from the MCU. The VRX regulator can also be controlled by the signal from the NASTA.

- VTX_ENA (from MCU) controls VTX regulator
- PSBS_ENA (from NASTA) controls VRX regulator

In addition PSA includes also functions listed bellow:

- Buffer for the M2BUS.
The buffer translates the logical input signal to open-drain output.

Table 10. M2BUS buffer truth table

Input	Output
LOW	LOW
HIGH	Z

- Power on/off and reset logic. The Power off logic can be used as a watchdog.
- Supply voltage monitor and automatic reset/power-off. VBATSW is internally divided and buffered battery voltage output. The A/D –converter input monitoring the battery voltage can be connected here. The circuit monitors the voltage at the VBAT input and forces the circuit to Reset if the voltage level is below allowed limit voltage, VBATcoff-. A hysteresis is included to prevent oscillation between different states.
- Battery charger detection. Externally divided charger voltage VCHAR goes through PSA internal switch to VCHARSW output. The A/D –converter input monitoring the charger voltage can be connected here.
- Automatic on-chip current limiting
- On-chip thermal shutdown, which protects PSA from overheating. Thermal shutdown includes hysteresis in order to prevent oscillation during the thermal protection.

Table 11. Regulators VA and VL characteristic

Parameter Test Conditions	Symbol	Limits			Unit
		Min	Typ	Max	
Output Voltage	VL, VA	2.73	2.82	2.90	V
Output current of the regulator (all regulators enabled)	Iout _{VL} Iout _{VA}	0 0	40 100		mA mA
Quiescent current VL: Iload = 0mA Iload = 40mA VA: Iload = 0mA Iload = 100mA	Iq			200 220 200 220	µA µA µA µA
Quiescent current Tamb = +25°C, VBAT=3.6V VL: Iload = 0mA Iload = 40mA VA: Iload = 0mA Iload = 100mA	Iq			110 130 110 130	µA µA µA µA
Quiescent current in Power-Off VL VA	Iqoff			6 15	µA µA
Line regulation: VL, VA Iout _{VL} = 40mA, Iout _{VL} = 100mA, 3.25V ≤ VBAT ≤ 5.2V	VL _{line} , VA _{line}		20		mV
Load regulation: VL, VA 0mA ≤ Iload _{VL} ≤ 40mA, 0mA ≤ Iload _{VA} ≤ 100mA, 3.25V ≤ VBAT ≤ 5.2V	VL _{load} , VA _{load}		30		mV

Table 11. Regulators VA and VL characteristic (continued)

Parameter Test Conditions	Symbol	Limits Min	Typ	Max	Unit
Line transient: AC=0.5V square wave Slew rate = 50 mV/ μ s $f = 500\text{Hz} \dots 2\text{kHz}$ $3.5\text{V} \leq \text{VBAT} \leq 5.2\text{V}$	VL_{linetr}, VA_{linetr}	40			dB
Load transient: VL, VA Iload _{VL} 100 μ A to 40mA, Iload _{VA} 100 μ A to 100mA in 10 μ s $3.25\text{V} \leq \text{VBAT} \leq 5.2\text{V}$	ΔV Trec Note 1		40 20		mV μ s
Current limit (VL,VA = 0V) VL VA	I _{lim}	60 150	180 450		mA mA
Power Supply Ripple Rejection $3.2\text{V} \leq \text{VBAT} \leq 5.2\text{V}$ $0\text{mA} \leq I_{loadVL} \leq 40\text{mA}$, $0\text{mA} \leq I_{loadVA} \leq 100\text{mA}$ $f = 10\text{Hz} \dots 10\text{kHz}$	PSRR	40			dB
Settling time Cload=1 μ F \pm 20% load current 0mA	t _s Note 2			160	μ s

Note 1: Voltage deviation (ΔV) is the output voltage overshoot in transient response. Recovery time (Trec) is the time from the beginning of the transient response to the time point when the regulator output voltage first crosses the final stable value after overshoot.

Note 2: Settling time is defined from the time point of mode change Power-Off to Reset to the time when regulator output voltage is within 5% of the final value.

Table 12. Regulators VRX and VTX characteristic

Parameter Test Conditions	Symbol	Limits Min	Typ	Max	Unit
Output Voltage	VRX, VTX	2.73	2.82	2.90	V
Output currents of the regulators (all regulators enabled)	Iout _{VRX} Iout _{VTX}	0.05 0.02	50 60		mA mA
Quiescent current VRX: Iload = 0A Iload = 50mA VTX: Iload = 0A Iload = 60mA	I _q			320 360 320 360	μ A μ A μ A μ A

Table 12. Regulators VRX and VTX characteristic (continued)

Parameter Test Conditions	Symbol	Limits Min Typ Max	Unit
Quiescent current Tamb = +25°C, VBAT=3.6V VRX: Iload = 0A Iload = 50mA VTX: Iload = 0A Iload = 60mA	Iq	180 195 180 195	µA µA µA µA
Quiescent current in Power-Off VRX VTX	Iqoff	14 17	µA µA
Line regulation: VRX, VTX IoutVRX = 50mA, IoutVTX = 60mA, 3.25V ≤ VBAT ≤ 5.2V	VRX _{line} , VTX _{line}	20	mV
Load regulation: VRX, VTX 50µA ≤ Iload _{VRX} ≤ 50mA, 20µA ≤ Iload _{VTX} ≤ 60mA, 3.25V ≤ VBAT ≤ 5.2V	VRX _{load} , VTX _{load}	30	mV
Line transient: VRX, VTX AC=0.5Vpp square wave Slew rate = 50 mV/µs f = 500Hz 2kHz 3.5V ≤ VBAT ≤ 5.2V	VRX _{linetr} , VTX _{linetr}	40	dB
Load transient: VRX, VTX Iload _{VRX} 50µA to 50mA, Iload _{VTX} 20µA to 60mA in 10µs 3.25V ≤ VBAT ≤ 5.2V	ΔV Trec Note 1	40 20	mV µs
Current limit (VRX, VTX = 0V) VRX VTX	I _{lim}	75 90 225 270	mA mA
Power supply ripple rejection 3.25V ≤ VBAT ≤ 5.2V 50µA ≤ Iload _{VRX} ≤ 50mA, 20µA ≤ Iload _{VTX} ≤ 60mA, f = 10Hz....10kHz f = 10Hz....50kHz f = 10Hz....100kHz	PSRR _{VRX, VTX}	50 40 35	dB dB dB
Settling time, Cload=1µF±20% load current 0mA	ts Note 2	100	µs

Note 1: Voltage deviation (ΔV) is the output voltage overshoot in transient response. Recovery time (Trec) is the time from the beginning of the transient response to the time point when the regulator output voltage first crosses the final stable value after overshoot.

Note 2: Settling time is defined from VTX_ENA/VRX_ENA rise to the time when regulator output voltage is within 5% of the final value.

Operation modes

The circuit has three operational modes: Power-Off, Reset and Power-On. The additional modes are the Protection mode and Battery disconnected ($V_{BAT} < V_{Rth}$, master reset threshold). Respective conditions of the external signals are described in the NO TAG.

Table 13. Operational modes

MODE	PURX	VRX_ENA	VTX_ENA	VL_VA	VRX	VTX	VBATSW	VCHAR_SW	PWRON-BUFF
Power-Off	LOW	X	X	Z	Z	Z	Z	Z	LOW
Reset	LOW	L	L	2.8V	Z	Z	Z	Z	LOW
	LOW	H	H	2.8V	2.8V	2.8V	Z	Z	LOW
Power-On	HIGH	L	L	2.8V	Z	Z	VBATSW	VCHAR	XPWRONX
		H	H	2.8V	2.8V	2.8V	VBATSW	VCHAR	XPWRONX

NOTE: VBATSW and VCHARSW are controlled by internal VSW_ENA– signal during power-on.

NOTE: PWRONBUFF is an inverted (and buffered) PWRONX. A logic LOW level at PWRONX (active LOW) will force a logic HIGH level at PWRONBUFF.

Power-Off Mode

In order to be in Power-Off mode V_{BAT} must be above V_{Rth} .

During Power-Off mode PURX is at logical low level. VA, VL, VRX and VTX regulators are disabled and in high-Z low output state.

Entering Power-Off Mode

The PSA contains a watchdog counter that is reset by writing "1" – "0" sequence to input PWROFFX.

The circuit goes to Power-off mode from Power-On after delay T_{off} if watchdog has not been reset during this time.

The other possibility to enter the Power-Off is from Reset, if the PSA can not enter Power-On mode because $V_{BATcoff+}$ is not reached. This means that watchdog elapses before the microcontroller is able to produce a pulse to PWROFFX. If charger is present ($V_{CHAR} > V_{CHARth}$), transition from Reset to Power-Off can not occur but the circuit stays in Reset mode as long as battery has been charged above $V_{BATcoff+}$.

The circuit goes to battery disconnected mode if battery voltage drops below master reset threshold (V_{Rth-}).

For testing purposes the watchdog can be disabled and reset by grounding the WD_DISX pin. In normal use it can be left floating (internal pull up).

Charging in Power–Off

Charging is not possible in Power–Off. Connecting a charger during Power–Off generates a rising edge on VCHAR input and the circuit enters Reset mode. Circuit stays in Reset as long as the battery is charged to the limit VBATcoff+.

If the watchdog elapses during Power–On when charger is connected, the circuit goes to Power–Off. Because charger detection is level sensitive, charger is detected and the circuit goes via Reset mode to Power–On mode.

Reset Mode

The circuit goes into Reset mode from Power–Off when:

- the battery voltage is initiated (master reset) or
- logic low voltage in PWRONX is detected or
- charger voltage becomes available or
- when recovering from Protection mode

In Reset mode the VL and VA outputs are activated by an internal enable signal. The VRX and VTX have external enable inputs VRX_ENA and VTX_ENA. VBATSW and VCHARSW are disabled and PURX is LOW.

The circuit leaves the Reset mode after a delay Trd for Power–On if $VBAT > VBATcoff+$. Watchdog is reset when Power–On mode is entered.

The circuit goes into Reset mode from Power–On when the battery voltage VBAT drops below VBATcoff–.

VBAT is monitored internally, hence if voltage VBAT drops below the threshold (determined by internal resistors), transition from Power–on to Reset mode is done. If VBAT doesn't rise back above reset release limit in time T_{off} the Watchdog elapses and the circuit powers off.

To avoid PSA going to RESET mode due to fast transient, transition from Power–On to Reset mode is not done if VBAT is below VBATcoff– for shorter time than threshold detection delay T_{dd} .

The circuit leaves the Reset mode after a delay T_{rd} if $VBAT > VBATcoff+$.

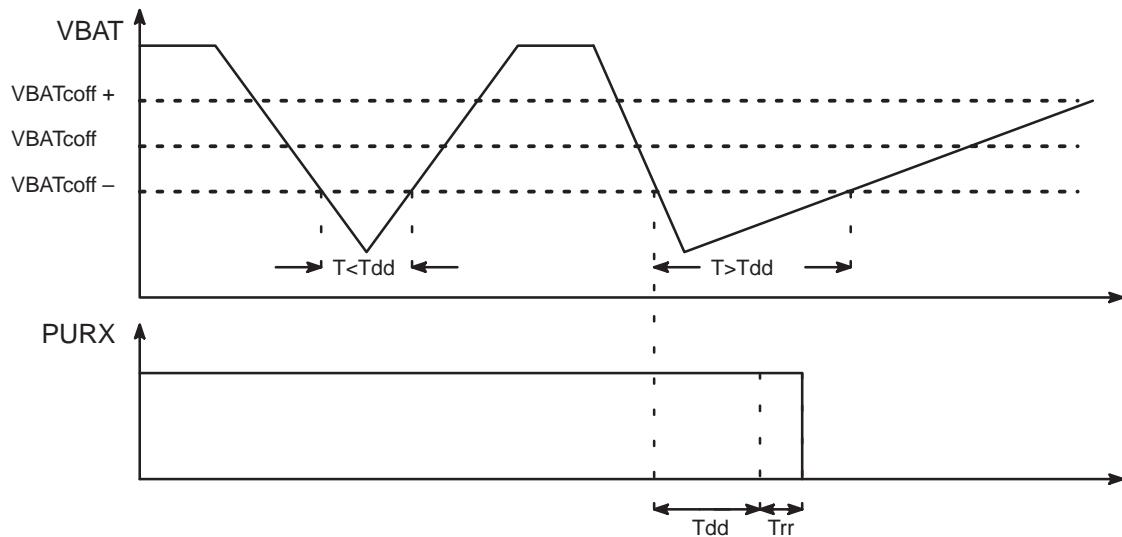


Figure 6. Threshold detection delay T_{dd} and PURX reaction time T_{rr}

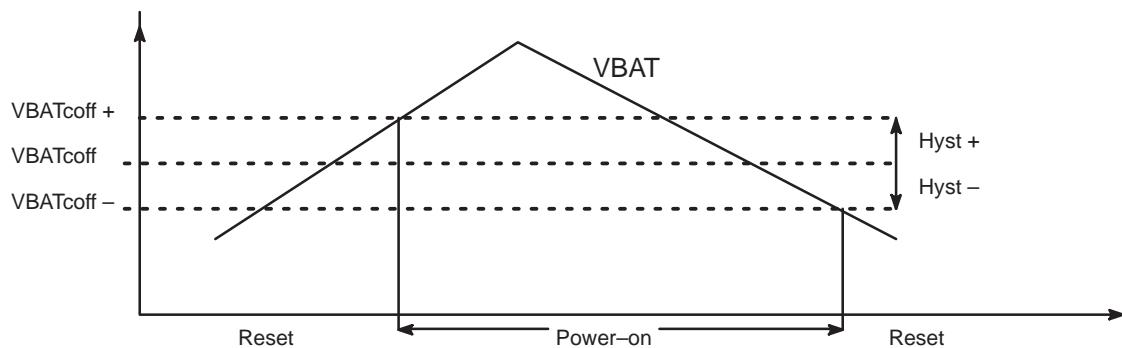


Figure 7. Reset limits and hysteresis

Power-On Mode

In Power-on mode all the functions are active. $V_{BATS W}$ and V_{CHARSW} outputs are activated by the internal enable signal V_{SW_ENA} . PURX is high in Power-On.

From Power-On mode the circuit goes to Power-Off mode after a delay T_{off} (watchdog delay set by an external capacitor C_{osc}) if no writing sequence to $PWRONX$ from logical high level to low level has detected during this time.

In Power_on mode the circuit does not react on PWRONX pulse i.e. the circuit must be switched off by the system by not updating the watchdog writing in time T_{off} .

AUDIO

Audio Control

Most of audio control is performed by the NASTA 4.5 IC, which contains audio and signalling processors. Internal and headset microphones signals are connected to same input of the NASTA via bilateral switch. The EAR signal of the NASTA is fed to an external amplifier (LM4862) with a dual ended type output. The XEAR signal of NASTA is carried to the transistor buffer.

Internal microphone

The internal microphone is connected to the bottom connector by means of mounting springs for automatic assembly. The microphone requires a bias current to operate. The bias current is generated in the NASTA.

Internal earphone

The internal earphone is connected to the UI board. The low impedance, dynamic type earphone is connected to a differential output of the audio amplifier (LM4862). Keypress and user function response beeps are generated with the internal earphone.

Buzzer

Alerting tones and/or melodies as a signal of an incoming call are generated with a buzzer that is controlled with a PWM signal by the MCU. The buzzer is a SMT device and is placed on the UI board.

Headset detection

The external headset device is connected to the system connector, from which the signals are routed via bilateral switch to the NASTA microphone input and via transistor buffer to the NASTA XEAR output. In the XMIC line there is a $47\text{ k}\Omega$ pullup in the transceiver. Resistance of the microphone is low compared to the transceiver pullup. When there is no call going the XMIC is pulled up. When a headset is connected, the XMIC is pulled down. The XMIC is connected to HSCON line which is one of MCU's A/D inputs. MCU is scanning the HSCON line and it detects both connection and disconnection. When headset is detected the headset microphone will get the DC bias current from transistor V740.

Headset Switch detection

In the XEAR line there is a $47\text{ k}\Omega$ pullup in the transceiver. Resistance of the earphone is low compared to the transceiver pullup. When a remote

control switch of the headset is open, there is a capacitor in series with the earphone, so the XEAR is pulled up by the phone. When the switch is closed, the XEAR is pulled down via the earphone. The XEAR is connected to HEADSW which is one of MCU input line. So both press and release of button gives an interrupt.

NASTA ASIC

The NASTA 4.5 is a single chip audio/signalling processor in a 64 TQFP package for AMPS and TACS systems.

Main features

- Single chip 2.8 V supply and Internal signal ground generation
- 8 bit parallel interface with pull ups
- Low noise microphone amplifier
- Input for a handset microphone or an accessory
- Microphone sensitivity compensation +4.8/-4.2 dB range (4 bits)
- Compandor
- RX and TX filters
- Tx hard limiters
- Internal reference compensation +1.00/-0.75 dB range(3 bits)
- Summing stage for voice and signalling data and SAT and ST
- Transmitter compensation amplifier with +3.75/-3.75 dB range (4 bits)
- TX speech max deviation trimmer with +1.75/-1.75 dB range (3 bits)
- Receiver compensation amplifier with +3.75/-3.75 dB range (4 bits)
- Volume control amplifier with -20/+17.5 range (4 bits)
- Earphone amplifier with drive capability for ceramic earpiece
- Buffered output for a handset or an accessory
- Audio mute switches
- Dual and single tone multifrequency generator
- 4.8 MHz oscillator/PLL-VCO circuitry for clock generation
- Driver for buzzer amplifier
- Hardware implemented hands free
- Synchronization to the received wide band signalling from base station
- Data validity detection
- Continuous word sync validity check
- Manchester encoding and decoding
- 3/5 majority vote and bch decoding for the received messages
- SAT filtering, detection and regeneration
- ST signal generation
- Transmitted data,ST and SAT filtering
- Programmable output clock with clock stop
- Low power consumption modes, Extended standby drivers
- Programmable timer
- AFC function

Table 14. Pin list of the NASTA ASIC

Pin no	Symbol	Pin type	Notes
1	VDD1		+ 2.8 V Supply voltage, digital
2	XRD	DIN/pu	Read control signal, active state LOW, pull-up > 50 kΩ
3	XCS	DIN/pu	Chip select signal, active state LOW, pull-up > 50 kΩ
4	A3	DIN	4-bit address bus, MSB
5	A2	DIN	4-bit address bus
6	A1	DIN	4-bit address bus
7	A0	DIN	4-bit address bus, LSB
8	D7	DIO	8-bit bidirectional data bus MSB
9	D6	DIO	8-bit bidirectional data bus
10	D5	DIO	8-bit bidirectional data bus
11	D4	DIO	8-bit bidirectional data bus
12	D3	DIO	8-bit bidirectional data bus
13	D2	DIO	8-bit bidirectional data bus
14	D1	DIO	8-bit bidirectional data bus
15	D0	DIO	8-bit bidirectional data bus LSB
16	VDD2		+ 2.8 V Supply voltage, digital
17	TOUT	DOUT	Test Output, Digital
18	XCLR	DIN	HW reset input, active state LOW
19	TMODE	DIN/pd	Test mode selection, pull-down > 50 kΩ
20	TSEL	DIN/pd	Test select, pull-down > 50 kΩ
21	XINT	DOUT	Interrupt request, active state LOW
22	SYNBIAS	DOUT	Synthetizer on/off control, HIGH = power on
23	RXBIAS	DOUT	Receiver on/off control, HIGH = power on
24	IF	AIN	IF input
25	VSS2		0 V Supply voltage, digital ground
26	VSA2		0 V Supply voltage, analog
27	DAF	AIN	Signal input
28	FILO	AOUT	Rxfilter output
29	EXPI	AIN	Expander input
30	EAMPBO	AOUT	Expander Amplifier B output
31	EWCI	AIN	Expander Window Comparator input
32	EXPO	AOUT	Expander output
33	VDA2		+ 2.8 V Supply voltage, analog
34	VOLI	AIN	Volume control ampl. input (Volume)
35	XEAR	AOUT	Buffered output for handset or an accessory
36	EVGND	AIN	Earphone driver virtual ground

Table 14. Pin list of the NASTA ASIC (continued)

Pin no	Symbol	Pin type	Notes
37	EARM	AOUT	Earphone driver output
38	EARP	AOUT	Earphone driver output
39	CWCI	AIN	Compander window control input
40	DACO	AOUT	DA converter output
41	SIDEAR	AOUT	Sidetone output
42	REF	AIN	Internal analog signal ground 1.40 V
43	MIC	AIN	Microphone amplifier input
44	BIMIC	AOUT	Microphone bias current output
45	CMIC	AIN	Microphone current stabilization capacitor
46	XMIC	AIN	Audio input for a handset or an accessory
47	ATTO	AOUT	Transmit HF attenuator output (TXATT)
48	VDA1		+ 2.8 V Supply voltage, analog
49	COMI	AIN	Compressor input
50	COMO	AOUT	Compressor output
51	EMPI	AIN	Pre emphasis input
52	EMPO	AOUT	Pre emphasis output
53	LPIN	AIN	Transmit lowpass filter input
54	ATST	AOUT	Audio Filter Test output
55	MOD	AOUT	Transmit path output
56	VSA1		0 V Supply voltage, analog
57	VSS1		0 V Supply voltage, digital ground
58	BUZZ	AOUT	Buzzer output
59	ATOUT	AOUT	Test pin
60	CLKOUT	COUT	14.85 MHz system clock output
61	CLKIN	CIN	14.85 MHz system clock input
62	CLKLCD	DOUT	Clock signal for LCD, 80 kHz, tristate when MCS1=MCS2=0
63	CLKMCU	DOUT	Clock signal for MCU, 4.8 MHz or 2.4 MHz
64	XWR	DIN/pu	Write control signal, active state LOW, pull-up > 50 kΩ

Transmit (TX) audio signal path

The TX audio signal is processed in the NASTA circuit and fed via the MOD line to the TX synthesizer on SYNTHESIZER module.

The NASTA ASIC contains the following stages for TX signal processing:

MICAM:

The signal input level from the microphone is 2.4mVrms nom., max. 40mVrms. The signal fed to this stage and amplified up to 200 mVrms.

TXMUX + TXAAF:

TX source selection (exmic/mic/dmmf/muted). Txaafil prevents aliasing in TXBP filter.

TXATT:

TXATT is a hands free attenuator. Maximum attenuation is selectable from four levels: -30, -27, -24 or -21 dB.

MICTRI:

MICTRI is for different microphone (phone microphone, headset and handset etc.) sensitivity compensation. It is used also for dtmf level setting. Gain 16 levels, step 0.6 dB, range -4.2 – +4.8dB.

BANDPASS:

Tx bandpass filter (300 – 3000Hz) filters high freq noise and low freq hum.

COMPR:

It compresses speech dynamic area to avoid noise at tx and radio path. It is a amplitude compressor and ratio is 2:1 in dB scale. It can be bypassed for measurement or dtmf purposes.

LIM1:

Hard limiter. It cuts the signal transients at +–439 mVpp levels.

PRE-EMP:

Pre-emphasis filter gives +6 dB/oct emphasis at the frequency band of 300 – 3000Hz.

LIM2:

Hard limiter. it cuts the signal transients at +–439mV levels.

TXLP:

The corner frequency of tx lowpass filter is 3000 Hz. Amplitude attenuation is 12 dB/oct after the corner point. Filter includes notch at 6 kHz.

TXTRI:

TXTRI is for nominal deviation tuning. Gain 8 levels, step 0.5 dB, range -+1.75dB.

TXPOSTFIL:

Postfil eliminates filter clock.

SUM:

SUM block makes d/a conversion of all generated signals. Then it sums all used signals and speech together.

WTRFIL:

This block is a lowpass filter for SAT, ST and data. Transmitter Compensation Amplifier is these too. Gain 16 levels, step 0.5 dB.

WPOSFIL:

WPOSFIL filters out the replicates of the output spectrum around WTRFIL clock frequency and its harmonics.

RECEIVE (RX) AUDIO SIGNAL PATH

The NASTA contains the following stages for RX signal processing:

RXTRI:

RXTRI is for demodulation sensitivity compensation. Gain 16 levels, step 0.5 dB, range $-+3.75\text{dB}$.

RXAAF:

RX aa filter filters out noise and other high frequency components from the incoming signal. It prevents aliasing in SATFIL and RXFIL.

RXMUX+AAFIL:

Rxmux selects speech from DAF-pin or DTMF from generator or all mute. Aafil prevents aliasing in RXFIL.

DEEMP+ RXFIL:

Rx filter filters out high frequency noise and low frequency hum. It has de-emphasis -6 dB/oct for the received speech signal (300–3000). There is a notch at 6kHz.

EXP:

Expands the speech dynamic back to normal. It is a amplitude expander and ratio is 1:2 in dB scale. It can be bypassed for measurement or DTMF purposes.

VOL:

VOL is for earphone or accessory speaker/earphone volume control. Volume Control Amplifier. Gain 16 levels over -20 to $+17.5\text{ dB}$ in 2.5 dB steps.

RXATT:

RXATT is a hands free attenuator. Maximum attenuation is selectable from four levels: -30 , -27 , -24 or -21 dB . Hands free controller (HF CONTR) measures peak-to-peak

level of the received audio and controls gains of the transmit and receive attenuators as a function of measured signal level.

EAR:

The earpiece amplifier is a single input, differential output amplifier for a ceramic earpiece.

ACC:

Buffer for accessory line is capable of driving high capacitive load. Gain and response of the buffer are fixed.

SIDEAR:

Audio output to be summed with EAR amplifier. Earphone amplifier gives extra +6dB gain to SIDEAR.

Transmitting data path

The data to be transmitted is loaded into the transmitting register DTR. From the DTR register the 8 bit data is fed into PISO-register, which changes the 8-bit data bytes to serial form. The serial NRZ-data is fed to the Manchester encoder (MANEN) and then to the summing block (SUM). Timing signals needed for data transmission are generated internally.

Receiving data path

The data from anti alias filter is connected through the comparator (DATAC) to a Manchester decoder (MANDEC) which decodes Manchester data to the NRZ (Non Return to Zero) format. The modem is synchronized to the receiving data with a digital phase locked loop (DPLL) and a word synchronization detection block (RECBUF). Data validity (DATVAL) is continuously detected (DFLAG), and this information is used internally when word synchronization detection is accepted. The serial data from the Manchester decoder is 3/5 majority voted (VOTE), BCH-decoded (BCH), corrected (CORR) and shifted to the receiver register (RREG). The final data word consists of 28 bits. 4 status bits are added to RREG to make up a 32 bit register, which is read in 8 bit bytes via status multiplexer (SMUX). The Receiver timing block (RECTIM) extracts the data from the received frames on control and voice channels and generates the data transfer interrupts (WFLAG). It also generates the repeat interrupts RFLAG. It maintains bit and word synchronization during different frames and passes the synchronization status (SFLAG) forward to the status register. On FOCC (Forward Control Channel) signalling mode it separates the multiplexed data streams (channel A and B) and Busy/Idle-information (XBOI). On FVC (Forward Voice Channel) signalling mode it extracts data repeats from voice channel message frames.

IF

The Intermediate Frequency Counter (IFCTR) is located on the modem to measure the frequency of IF signal.

AFC

The AFC makes the synthesizer fine tuning. It can be used for channel side-step also.

The AFC DA-converter output DC level tunes the RF oscillator (VCXO).

ST signalling tone generator

The signalling tone generator is two bit D/A converter that produces an 8 kHz sine wave. The tolerance of the frequency is ± 1 Hz.

Receiving SAT path

The SAT signal is filtered and amplified with a bandpass filter (SATFIL). SATFIL (Supervisory Audio Tone input FILter) is a 6 kHz bandpass filter. It separates the 5970, 6000, 6030 Hz SAT signal from the incoming voice and noise during voice channel operation. The signal is converted to digital square wave signal with a comparator (SATCOMP). The SAT detection is executed with a digital PLL/detection circuitry (SATDET). The logic compares the SCC code given by control register bits SCC0 and SCC1 to the incoming SAT frequency and indicates the result with a status register bit (SATVAL). The regenerated SAT is then fed to summing block (SUM).

Clock divider

The main function of the NASTA baseband clock generator is to generate a 4.8 MHz clock signal with selectable frequency shift (approx. 80 ppm) from 14.85 MHz master clock.

NHX-7 employs a 2.4 MHz clock for MCU (CLKMCU) and a 80kHz kHz clock for LCD display CLKLCD.

Standby Modes for Power Saving

The normal standby mode (receiver and synthesizer are continuously ON, audio paths OFF) is automatically activated when the circuit is initialized working in control channel ($COXV = 1$) and the extented standby is disabled ($ESTDBY = 0$).

The extented standby mode (receiver and synthesizer ON/OFF times controlled by the NASTA) is activated when the circuit is initialized working in control channel, extented standby is enabled and synthesizer and receiver hardware controls are enabled ($COXV=ESTDBY=SPHE=RPHE=1$). In extented standby mode the interrupts from control filler messages can be masked ($FIME=1$). The maximum number of consecutive received filler messages without interrupt is 31. After the interrupt the number of masked interrupts (filler) is available in SRB (RFMC0...4).

RF Section

Technical Summary

The purpose of the RF sub-module is to receive and demodulate the radio frequency signal from a base station and transmit modulated RF signal to a base station. The RF section comprises the RX-submodule, the TX submodule and the Synthesizer submodule.

EMC leakage is prevented with sheet metal boxes covering the critical blocks of the transceiver.

Basic Specification

Table 15. Basic Specifications

Parameter	Value
RX frequency band	917 – 950 MHz
TX frequency band	872 – 905 MHz
RX LO frequency band	962 – 995 MHz
Duplex spacing	45 MHz
Channel numbers	1329...2047, 0...600
Number of channels	1320
Channel spacing	25 kHz
TX output power	6 levels; 6.5 (+2/-4) dBm to 26.5 (+2/-4) dBm
Method of frequency synthesis	Dual PLL with two UHF signals for RX LO and TX
Frequency control	AFC with +/- 2.5 kHz limits
Receiver type	Superheterodyne with double IF
Modulator type	FM-modulator
Current consumption, reception	50 mA
Current consumption, standby	30 mA
Current consumption, transmission	550 mA

RF Module Characteristics

Maximum ratings

The maximum battery voltage during transmission must not exceed 5.85 V. Higher battery voltages may destroy the power amplifier module.

Table 16. Maximum ratings

Parameter	Value
Battery voltage (Ni-Mh Battery)	nom. 3.6 V, min. 3.1 V, max. 4.6 V
Battery voltage (Li-Ion Battery)	nom. 3.6 V, min. 3.1 V, max. 4.1 V
Regulated supply voltage	2.82 V +/- 0.09V
Operating temperature range	-10 ... +55 deg.C

DC Characteristics

Regulator

The PSA regulator module in the BB unit regulates voltages VA, VRX and VTX to the fixed 2.82 V level for the RF unit.

Battery Save at Reception Mode

The receiver and receiver synthesizer blocks are switched on/off during stand-by mode. This switching is controlled by the NASTA – audio module. If the received signal is strong enough, it switches PSA's VRX_ENA off for about half of time. This powers down all the receiver blocks and RX-VCO. Also the synthesizer module is switched to power off mode during battery save.

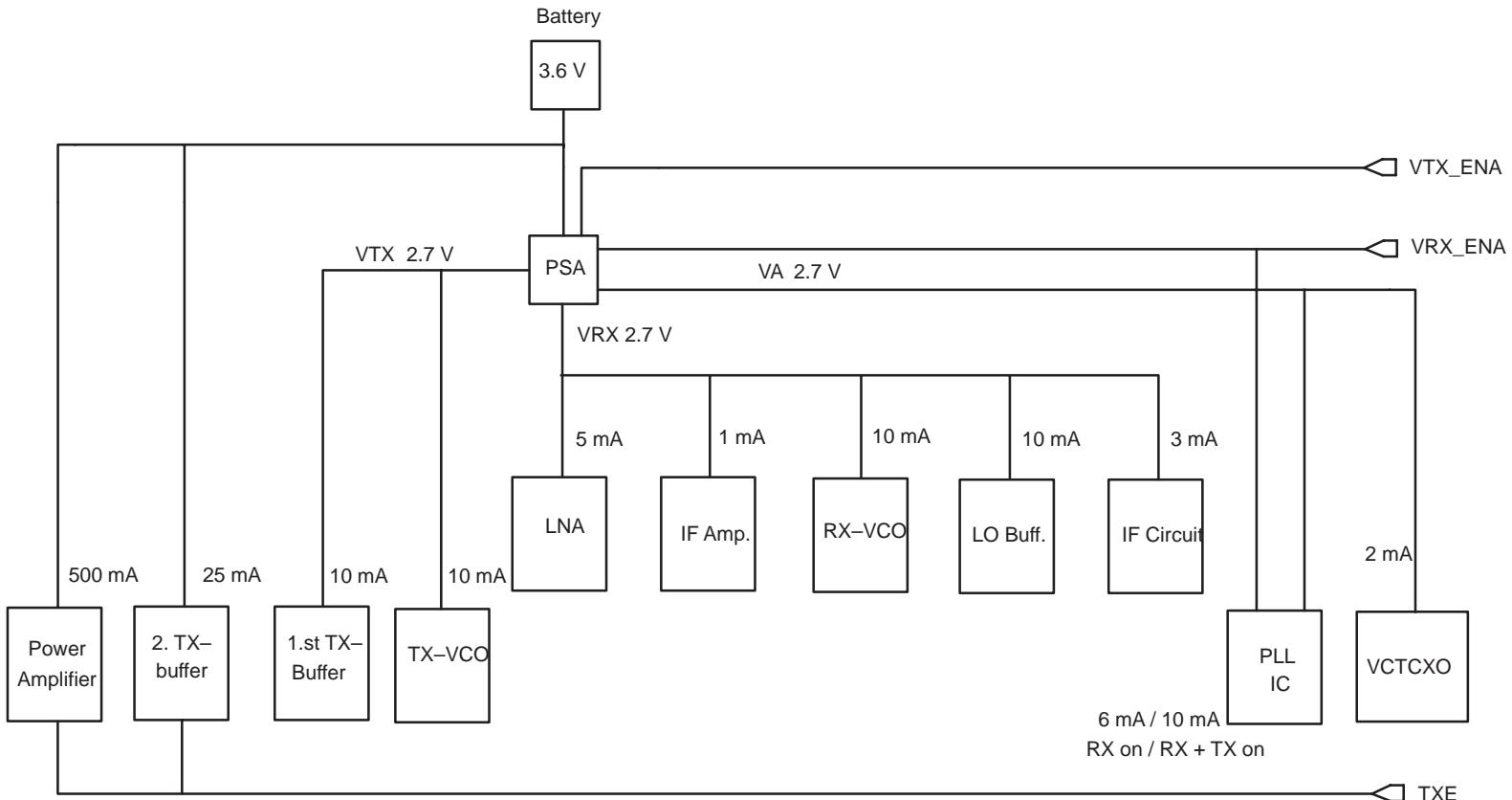
Control Signals

The following table describes the RF current consumption with different status of the control signals. RX and TX synthesizer phase locked loops are switched on/off by a control byte that is loaded to the PLL circuit.

Table 17. Control Signals and Current Consumption

VRX_ENA + SW powerup for RX synthesizer	VTX_ENA + SW powerup for TX synthesizer	TXE	Typical Current Consumption /mA	Note
H	H	H	550 mA	Power Level 2
H	H	L	70 mA	
H	L	L	50 mA	Synthesizer TX part has been powered off
L	L	L	8 mA	All RF parts have been powered off

Power Distribution Diagram



Connections

Connections to Baseband module

Signal Name	Type	Function
AFC	Analog out	The reference oscillator frequency adjust.
DAF	Analog in	Demodulated received signal (audio + data)
GND	Power	Common ground
IF	Analog out	2nd IF signal (450 kHz)
MOD	Analog out	Modulation signal for transmitter (audio + data)
RSSI	Analog in	Received signal strength indicator. Voltage measurement.
SCLK	Digital out	Serial clock for synthesizer. Active state: Rising edge
SDAT	Digital out	Serial data for synthesizer. Active state: High
SLE	Digital out	Synthesizer latch enable. Active state: Low
HPD_EN	Digital out	PLL Hardware power down
RXS_LD	Digital in	RX-synthesizer lock detect
TXC	PWM out	Transmitter power control
TXE	Digital out	Transmitter enable. Active state: High
TXI	Analog in	"TX power on" –indicator
VA	Power	Regulated voltage to synthesizer circuit and VCTCXO
VBAT	Power	Battery voltage to transmitter
VRX	Power	Regulated voltage to receiver
VTX	Power	Regulated voltage to TX-VCO, 1st.TX-LO buffer and power control circuit

Values for digital control signal		
Supply voltage	VDD	2.7 V
Logical 1	VOH	>VDD*0,7
Logical 0	VOL	<VDD*0,3
Logical 1	IOH	<1mA , 1µA (typical)
Logical 0	IOL	<1mA , 1µA (typical)

CLKIN	VCTCXO signal
Frequency	14.85 MHz
Level	1 Vpp (0.7 Vpp Min.)
Load impedance	% 5 kΩ //20 pF (Typical)
Start time	45 ms after VA rising

AFC	VCTCXO control voltage
Type	analog signal (DC-level)
Level	0.3...2.5 V DC
Source impedance	$Z_s < 1.5 \text{ kohm}$
Load impedance	10 kohm // 10 pF ± 10 %
Control step size for TX freq.	100 Hz (typical)

DAF	Demodulated audio and data signal
Type	analog signal
Nominal level	50 mVrms @ 2,3 kHz deviation
Unit to unit variation	35 mV...65 mV
Source impedance	$Z_S < 5 \text{ kohm}$
Load impedance	$Z_L > 50 \text{ kohm}$

IF	450 kHz 2nd IF signal
Level	250 mVpp (typical) not specified by manufacturer
Source impedance	< 500 Ω
Load impedance	> 7 k Ω

MOD	Modulation signal for transmitter (Audio + data)
Type	Analog signal
Nominal level	200 mVrms @ 2.3 kHz deviation
Load impedance	$Z_L > 50 \text{ kΩ}$
Source impedance	$Z_s < 2.5 \text{ kΩ}$

RSSI	Received signal strength indicator
DC-level	0.2...2.3 V
Source impedance	56 kΩ (typical)

SCLK	Serial clock for synthesizer
Type	digital signal
Pulse width	> 1 us

SDAT	Serial data for synthesizer
Type	digital signal
Pulse width	> 1 us
VALUES:	

SDAT	Serial data for synthesizer	
Control byte		x110 011x x001 11xx (x = don't care bit)
Reference divider		1188
Divider formulas for RX oscillator (ch 1329...2047)		$N = 2 * (ch - 1329) + 73361$
Divider formulas for RX oscillator (ch 0...600)		$N = 2 * ch + 78399$
Divider formulas for TX oscillator (ch 1329...2047)		$N = 2 * (ch - 1329) + 69761$
Divider formulas for TX oscillator (ch 0...600)		$N = 2 * ch + 71199$

SLE	Synthesizer enable	
Type		Digital signal
Function		0 = synthesizer enabled 1 = synthesizer disabled

HPD_EN	PLL Hardware power down	
Type		Digital signal
Function		0 = Power down enabled 1 = Power down disabled

RXS_LD	RX-Synthesizer lock detect	
Type		Digital signal
Function		0 = Unlocked 1 = Locked

TXC	Transmitter power control	
Type		PWM signal
Function		Duty cycle of the TXC signal defines the TX power level
PWM frequency		9.4 kHz
Number of duty cycle steps		256
Load impedance		> 100 kohm

TXE	Transmitter on/off control	
Type		Digital signal
Function		0 = TX off 1 = TX on

TXI	"TX power on" –indicator	
Type		Analog signal
Source impedance		33 kΩ
Level		< 1 V = TX off > 1 V = TX on

VA	Regulated voltage for synthesizer	
Nominal value		2.7 V ± 4%
Max. current		100 mA

VBAT	Battery voltage	
Nominal value		3.6 V
Minimum value		3.1 V
Absolute maximum		4.6 V
Max. current		800 mA

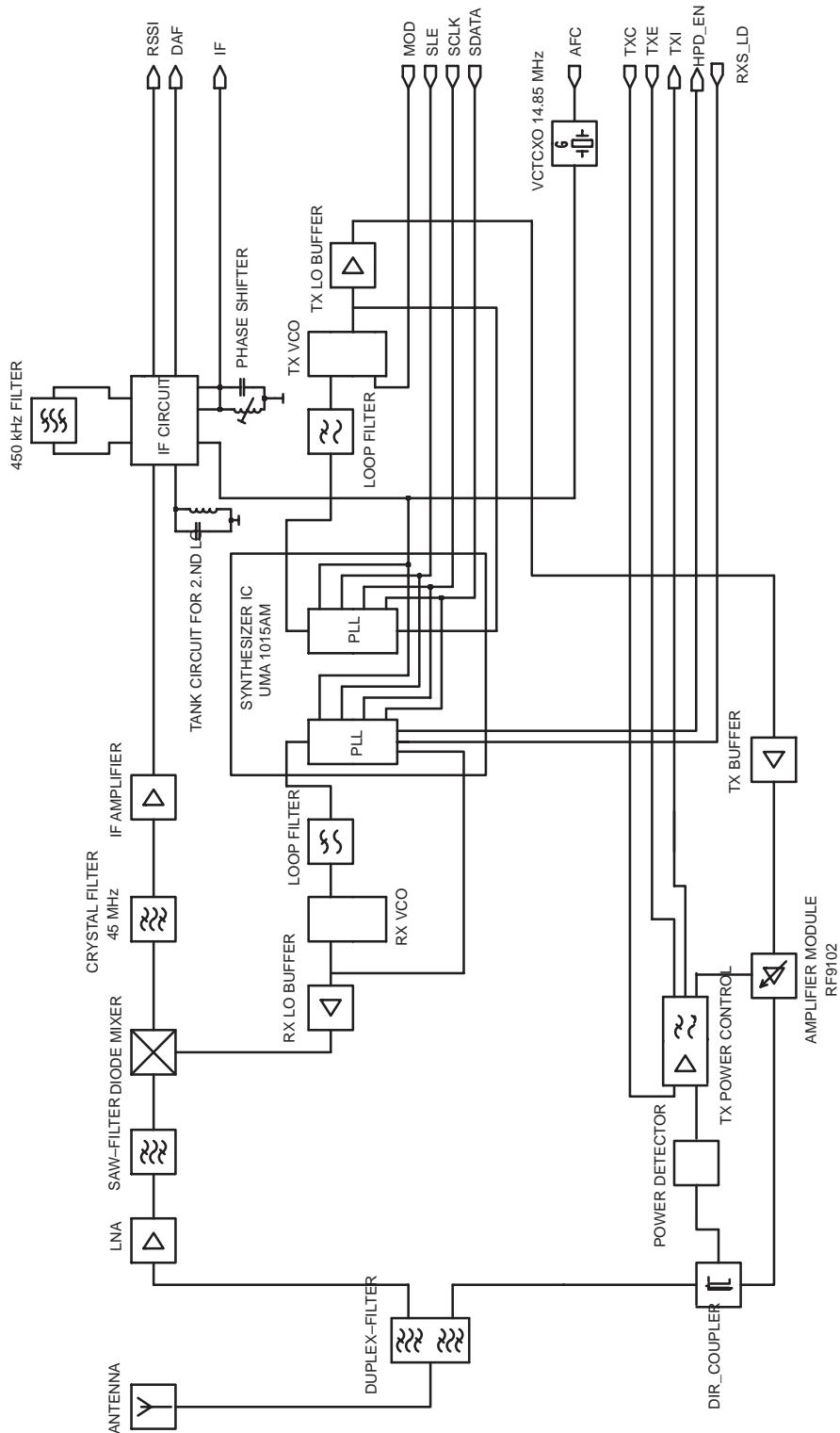
VRX	Regulated voltage for receiver	
Nominal value		2.82 V (-0.09V /+0.08V)
Max. current		50 mA
VTX	Regulated voltage for TX	
Nominal value		2.82 V (-0.09V /+0.08V)
Max. current		60 mA

Antenna

The phone includes a helix antenna. The electrical length of the helix antenna is 3/8 wave length.

Functional description of radio sub-module

Block diagram



RF components

Antenna:	0660184
Antenna clip:	9510480
Duplexer:	4512085
45 MHz IF filter:	4510129
450 kHz IF filter:	4550045
SAW filter:	4511034
VCTCXO:	4510171
FM detector IC:	4349694
PLL IC:	4340393
RX VCO:	4350113
TX VCO:	4350115
Power amplifier:	4370099

Receiver

The receiver is a dual-conversion superheterodyne using two intermediate frequencies, 45 MHz and 450 kHz.

The RF signal from the duplexer RX port is applied to the RF amplifier.

Next the signal is filtered with SAW-filter Z321. The filter is followed by a single balanced diode mixer, which has 6 dB conversion loss.

After that mixer signal is filtered with the crystal filter Z350, which has 15 kHz bandwidth. Next the IF signal is amplified by V380. From the amplifier the IF-signal is applied to the second mixer.

The second mixer, the LO buffer transistor, IF amplifier and quadrature detector are all integrated in the circuit N370. The second LO frequency, 44.55 MHz, is third harmonic of the VCTCXO frequency. LO signal is realized with tank circuit C372 and L371. After the mixer the 450kHz IF signal is filtered with ceramic filter Z370. The IF amplifier output signal is phase shifted by resonance circuit. After this the signal is fed to a quadrature detector.

Signal DAF is low pass filtered by R372 and C379. The DAF, RSSI and 2nd IF signal (450 kHz) are fed to the audio/logic unit.

During battery-save mode the voltage VRX is down and all the receiver blocks and the RX synthesizer are powered down.

RX Synthesizer

The first injection frequency for receiver is generated by a digital phase locked loop (PLL). The output frequency of the loop (LO) is obtained from a voltage-controlled oscillator (VCO) G530. The VCO output signal is amplified by RX-LO-buffer and fed to the receiver mixer. The injection level required by the receiver mixer is about +3 dBm. In addition, the signal is fed back to the dualsynthesizer circuit N820.

The overall divisor of the chain is selected according to the desired channel.

The internal dividers of N820 are programmed with 17 bits, which are transferred serially on the SDAT (synthesizer data) line from the processor into an internal shift register also located in N820. Data transfer is timed with SCLK clock pulses.

The divided frequency is compared with a highly stable reference frequency by a phase comparator in the PLL circuit. The phase comparator controls the VCO frequency by means of a DC voltage through the loop filter so as to keep the divided frequency applied to the phase comparator equal to the fixed reference frequency.

The reference frequency is 12,5 kHz. This reference frequency is obtained from voltage controlled crystal oscillator (VCTCXO). Oscillator frequency is 14.85 MHz. The VCTCXO frequency is divided by 1188.

RX loop filter

Phase comparator output is pin 3. If the VCO (G530) frequency is too high, the output goes low and discharge integrator capacitor C521. After this, the DC control voltage and the VCO frequency will decrease.

If the VCO frequency is too low, the output goes high and charge the integrator capacitors C522 and C523. Thereafter the DC control voltage and the VCO frequency will go up.

Output pulses from the phase detector have to be supplied to the loop filter. The function of the integrator is to convert positive and negative pulses to DC voltage. The remaining ripple and AC components are filtered in the lowpass filter.

TX Synthesizer

The transmitter synthesizer generates a frequency modulated transmitter signal for the transmitter section. The modulated TX injection frequency is generated in TX-VCO (G430). The TX modulated TX signal is amplified in TX-buffer before the transmitter.

TX Loop Filter

Output pulses from the phase detector N820 pin 17 have to be supplied to the loop filter. The integrator, which consists of R420 and C421, converts positive and negative pulses to DC voltage. The remaining ripple is filtered in the low-pass filter.

Transmitter

The transmitter comprises a power amplifier module. The modulated RF signal from the TX synthesizer is applied to the 50 ohm input of the module. The power level is controlled by the voltage supplied to the pin 8. Amplifier module has two output pins (pins 13 and 12). The real part of the output impedance is 7 ohms. The amplified RF signal is fed to the duplex filter via

a 50 ohm impedance matching circuit. Harmonics generated by the transmitter are attenuated in the matching circuit and duplex filter. A voltage proportional to the output power is rectified from a directional coupler by DC-biased Schottky diode V640. This rectified voltage is fed to a differential amplifier which consists of transistor V650. The reference voltage is filtered from the PWM signal provided by the TXC line. The differential amplifier adjusts the control voltage so that the reference voltage and the voltage proportional to the output power are equal. The transmitter is switched on when TXE goes high (logic 1). TXE enables the transmitter power control circuit by transistor V641. When the transmitter is inactive (TXE low) the RF level from the transmitter is reduced below –60 dBm.

RF Characteristics

Temperature range	Minimum	Typical / Nominal	Maximum	Unit / Notes
Operating temperature	–10		+55	°C

Duplexer

	Transmitter		Receiver	
Frequency	872...905 MHz		917...950 MHz	
Insertion loss max	3.5 dB		4.8 dB	
Ripple at BW max	3.0 dB		3.0 dB	
Termination im-pedance	50 Ω		50 Ω	
Permissible input power	2.0 W		1.0W	
Returnloss at BW	12 dB		10 dB	
	Frequency [MHz]	Att. [dB]	Frequency [MHz]	Att. [dB]
Attenuation min				
	917...950	40	872...905	48
	1744...1810	40	962...995	10
	2616...2715	30	1007...1040	25

RX submodule

RX Specification

N=Normal E=Extreme conditions		Unit / Notes
	Frequency range	917...950 MHz
	Type	FM receiver, 2 IFs
	Intermediate Frequencies	45 MHz, 450 kHz

RX Specification (continued)

N=Normal E=Extreme conditions		Unit / Notes
N	RF-sensitivity	< -110 dBm (SINAD 20 dB)
E	RF-sensitivity	< -107 dBm (SINAD 20 dB)
N / E	Adjacent channel selectivity	>55 dB (25 kHz)
N	Spurious response rejection	> 55 dB
N	Intermodulation rejection	> 55 dB
Blocking:		
N	RX-band excluding the receive freq ±1 MHz	>-50 dBm
N	Bands 895 – 905 MHz and 970 – 980 MHz	>-23 dBm
N	Spurious emissions:	
N	100 kHz ... 1000 MHz	< -57 dBm
N	1000 MHz ... 4000 MHz	< -47 dBm
N	RX-band	< -70 dBm
N	TX-band	< -60 dBm
N / E	Audio harmonic distortion	< -30 dB (third harmonic)
N/E	Noise & Hum	< -32 dB
Audio frequency response		
N	300 Hz...500 Hz	+0.5/-1 dBm
N	500 Hz...2 kHz	±0.5 dB
N	2 kHz...3 kHz	+0.5/-1 dB
N	10 kHz	-6 dB (max.)
N / E	RSSI dynamic range	> 65 dB
N /E	RSSI starting level	> -113 dBm /-110 dBm
N/E	RSSI linearity	< 5 (10) dB

Preamplifier

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Supply voltage		2.7		V
Frequency band	917		950	MHz
Current consumption		5.5	6.5	mA
Insertion gain	14	15	16	dB
Gain flatness		±0,5		dB
Noise figure			2.3	dB
Reverse isolation	20			dB

	Minimum	Typical / Nominal	Maximum	Unit / Notes
IIP3	-8,0			dBm
Input return loss ($Z_0=50\Omega$)	10			dB
Output return loss ($Z_0=50\Omega$)	10			dB

SAW-filter

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Center frequency, f_0		933,5		MHz
Bandwidth		$\pm 16,5$		MHz
Attenuation:				
DC – 850MHz	35			dB
850 – 900 MHz	25			dB
900 – 905 MHz	10			dB
962 – 970 MHz	8			dB
970 – 1007 MHz	18			dB
1007 – 1010 MHz	30			dB
1010 MHz – 1.5 GHz	35			dB
1.5 – 3.0 GHz	15			dB
Insertion loss		4.0	5.0	dB
Passband ripple			1.0	dB
VSWR in passband			2.5	
Termination impedance		50		Ω

1st mixer

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Frequency band				
RF	917		950	MHz
LO	962		995	MHz
IF		45		MHz
Conversion loss			9	dB
IIP3	5			dBm
LO power level	3	5	7	dBm
LO-RF isolation	22	30		dB

1st IF-filter

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Type				2-pole
Center frequency, f_0		45,000		MHz
Passband width (at -3dB)	$f_0 \pm 15$ kHz			kHz
Stopband attenuation	12			dB at $f_0 \pm 50$ kHz
Stopband attenuation	65			dB at $f_0 - 900$ kHz
Spurious response rejection	10			dB
Insertion loss			3	dB
Passband ripple			1	dB
Terminating impedance		800 // 1,5		$\Omega // pF$
Group delay distortion		10		μs at $f_0 \pm 15$ kHz
Case				SMD

IF-amplifier

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Operating frequency		45		MHz
Supply voltage	2,7		3,0	V
Input impedance		800 // 1.5		$\Omega // pF$
Output impedance		1000		Ω
Current consumption		1		mA
Insertion gain (voltage)		10		dB
Noise figure			3	dB
IIP3	-30			dBm

2nd IF filter

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Center frequency		450		kHz
6 dB bandwidth	± 12.5			kHz
50 dB bandwidth			± 24	kHz
Insertion loss			4.0	dB

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Ripple			3.0	dB
Spurious response rejection	35			dBm
Input & output impedance		1500		Ω

IF-circuit

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Supply voltage	2.0		2.6	V
Current consumption			4.6	mA
Input resistance		5500		Ω
Input capacitance		2,8		pF
Mixer output resistance	-20 %	1800	+20 %	Ω
Noise figure			10	dB at 45 MHz
3rd order intercept point	-11			dBm
Mixer conversion gain	15	18	21	dB
2. lo frequency		44.550		MHz
2. lo injection level	90			$\text{dB}\mu\text{V}$
2. lo input impedance	10			$\text{k}\Omega$
2. lo harmonic level			-6	dBc
AM-rejection		40		dB ($V_{in}=80 \text{ dB}\mu\text{V}$)
RSSI dynamic range	60			dB
Case				16 SSOP

TX submodule

TX Specification

N=Normal E=Extreme conditions		Unit / Notes
	Frequency range	872 ... 905 MHz
N / E	Output power (after duplex filter) at all channels	
N / E	PL 0,1,2	26.5 (+2/ -4) dBm
N / E	PL 3	22.5 (+2/ -4) dBm
N / E	PL 4	18.5 (+2/ -4) dBm
N / E	PL 5	14.5 (+2/ -4) dBm

TX Specification (continued)

N=Normal E=Extreme conditions		Unit / Notes
N / E	PL 6	10.5 (+2/ -4) dBm
N / E	PL 7	6.5 (+2/ -4) dBm
N / E	Carrier switching time to within ± 3 dB of specified output power and frequency within ± 2.5 ppm of final frequency	< 2 ms
N / E	Carrier switching time from full power to -60 dBm	< 2 ms
N / E	Power level transition time (within 3 dB from any power level)	< 20 ms
	Spurious emissions	
N	100 kHz ... 1000 MHz	< -36 dBm
N	1000 MHz ... 4000 MHz	< -30 dBm
N	RX-band	< -70 dBm
N	TX-band (except ± 50 kHz Ft)	< -36 dBm
	Modulation bandwidth outside the region	
N	± 17 kHz	< -26 dBc
N	± 37.5 kHz	< -45 dBc
N	± 50 kHz	< -60 dBc

Power amplifier

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Supply voltage	3.15	3.6	5.85	V
Current consumption		550		mA (at $P_{out} = 1,2$ W)
Input power	+4	+6	+9	dBm
Output power	30	31	33	dBm
Efficiency	50			% (at operation point)
Harmonic level			-30	dBc (at $2*f_{carrier}$)
Harmonic level			-45	dBc (at $3*f_{carrier}$ and higher)
Spurious mixing loss at output	9	10		dB ($f_{carrier} \pm 45$ MHz)
Output SWR			No damage	

Power control circuit

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Supply voltage	3.15	3.6	4.6	V
Drive current			10	mA
Power control range	20			dB

Synthesizer submodule

PLL circuit for RX local oscillator signal and TX injection

PLL Synthesizer specification

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Frequency band (RX LO)	962		995	MHz
Frequency band (TX)	872		905	MHz
Channel separation		25		kHz
VCTCXO frequency		14.85		MHz
VCTCXO input level		1		Vpp (10kΩ)
Frequency stability			± 2.5	ppm
RF signal level from VCO to prescaler	50			mVrms
Supply voltage	2.7			V
Current consumption		8.5		mA

RX local oscillator signal

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Frequency band	962		995	MHz
Output level	+3	+5	+7	dBm / 50 Ω
Output return loss		10		dB
Phase noise		-112		dBc / Hz (25 kHz)
Tuning voltage limits	1		4	V
Tuning voltage at center frequency		2.5		V
Tuning voltage sensitivity	15	18	21	MHz / V
Temperature stability		± 10		MHz (all conditions)
Locking time to ±1 channel			20	ms

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Locking time to any channel			40	ms
RF signal level from VCO to prescaler	50			mVrms
Supply voltage	2.7			V
Current consumption		22		mA

TX VCO

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Frequency band	872		905	MHz
Output level	-3	0	+3	dBm / 50 Ω
Output return loss		10		dB
Phase noise		-102		dBc / Hz (25 kHz)
Tuning voltage limits	0		4	V
Tuning voltage at center frequency		2,5		V
Tuning voltage sensitivity	15	18	21	MHz / V
Locking time to ± 1 channel			20	ms
Locking time to any channel			40	ms
Modulation				
Input impedance		100		kΩ
deviation error			±10	% (in all conditions)
mod. frequency	0,3		10	kHz
mod. sensitivity		200		mVrms (2.3 kHz dev.)
RF signal level from VCO to prescaler	50			mVrms
Supply voltage	2.7			V
Current consumption		10		mA

TX buffers

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Frequency range	872		905	MHz
1.st buffer				
Output level	-2		4	dBm

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Supply voltage	2.7			V
Current con–sumption		10		mA
2.nd buffer				
Output level	8		12	dBm
Supply voltage	3.1	3.6	4.6	V
Current con–sumption		35		mA

VCTCXO

	Minimum	Typical / Nominal	Maximum	Unit / Notes
Frequency		14.85		MHz
Control voltage	0.5		2,5	V
Controlled frequency area		$f_0 \pm 1,25$		Hz
Control step		1.5		Hz
Frequency accuracy			± 2.5	ppm (all conditions)
Output level		1		Vpp
Supply voltage	2.7			V
Current consumption		2		mA

Parts list of JP3 (EDMS Issue 4.3)

Code: 0201185

ITEM	CODE	DESCRIPTION	VALUE	TYPE
R102	1422881	Chip resistor	0.22	5 % 1 W 1218
R105	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R106	1430187	Chip resistor	47 k	1 % 0.063 W 0402
R107	1430764	Chip resistor	3.3 k	5 % 0.063 W 0402
R110	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R111	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R140	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R141	1430788	Chip resistor	22 k	5 % 0.063 W 0402
R142	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R143	1430145	Chip resistor	100 k	1 % 0.063 W 0402
R144	1430145	Chip resistor	100 k	1 % 0.063 W 0402
R145	1430842	Chip resistor	680 k	1 % 0.063 W 0402
R146	1430842	Chip resistor	680 k	1 % 0.063 W 0402
R147	1430788	Chip resistor	22 k	5 % 0.063 W 0402
R148	1430766	Chip resistor	3.9 k	5 % 0.063 W 0402
R149	1430780	Chip resistor	12 k	5 % 0.063 W 0402
R161	1430770	Chip resistor	4.7 k	5 % 0.063 W 0402
R162	1430770	Chip resistor	4.7 k	5 % 0.063 W 0402
R163	1430734	Chip resistor	220	5 % 0.063 W 0402
R172	1430770	Chip resistor	4.7 k	5 % 0.063 W 0402
R202	1430145	Chip resistor	100 k	1 % 0.063 W 0402
R203	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R206	1430754	Chip resistor	1.0 k	5 % 0.063 W 0402
R207	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R208	1430690	Chip jumper		0402
R210	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R211	1430776	Chip resistor	8.2 k	5 % 0.063 W 0402
R212	1430690	Chip jumper		0402
R231	1430121	Chip resistor	22 k	1 % 0.063 W 0402
R232	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R241	1430790	Chip resistor	27 k	5 % 0.063 W 0402
R251	1430792	Chip resistor	33 k	5 % 0.063 W 0402
R252	1430792	Chip resistor	33 k	5 % 0.063 W 0402
R261	1430754	Chip resistor	1.0 k	5 % 0.063 W 0402
R262	1430832	Chip resistor	2.7 k	5 % 0.063 W 0402
R320	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R322	1430744	Chip resistor	470	5 % 0.063 W 0402
R323	1430772	Chip resistor	5.6 k	5 % 0.063 W 0402
R333	1430700	Chip resistor	10	5 % 0.063 W 0402
R340	1430776	Chip resistor	8.2 k	5 % 0.063 W 0402
R341	1430770	Chip resistor	4.7 k	5 % 0.063 W 0402
R342	1430700	Chip resistor	10	5 % 0.063 W 0402
R343	1430734	Chip resistor	220	5 % 0.063 W 0402

R361	1430778	Chip resistor	10 k	5 % 0.063 W	0402
R362	1430778	Chip resistor	10 k	5 % 0.063 W	0402
R363	1430756	Chip resistor	1.2 k	5 % 0.063 W	0402
R366	1430714	Chip resistor	33	5 % 0.063 W	0402
R370	1430758	Chip resistor	1.5 k	5 % 0.063 W	0402
R371	1430770	Chip resistor	4.7 k	5 % 0.063 W	0402
R372	1430762	Chip resistor	2.2 k	5 % 0.063 W	0402
R373	1430714	Chip resistor	33	5 % 0.063 W	0402
R381	1430770	Chip resistor	4.7 k	5 % 0.063 W	0402
R420	1430774	Chip resistor	6.8 k	5 % 0.063 W	0402
R421	1430786	Chip resistor	18 k	5 % 0.063 W	0402
R422	1430690	Chip jumper		0402	
R423	1430690	Chip jumper		0402	
R430	1430718	Chip resistor	47	5 % 0.063 W	0402
R431	1430734	Chip resistor	220	5 % 0.063 W	0402
R434	1430700	Chip resistor	10	5 % 0.063 W	0402
R440	1430720	Chip resistor	56	5 % 0.063 W	0402
R441	1430774	Chip resistor	6.8 k	5 % 0.063 W	0402
R442	1430764	Chip resistor	3.3 k	5 % 0.063 W	0402
R443	1430700	Chip resistor	10	5 % 0.063 W	0402
R444	1430744	Chip resistor	470	5 % 0.063 W	0402
R450	1430726	Chip resistor	100	5 % 0.063 W	0402
R451	1430770	Chip resistor	4.7 k	5 % 0.063 W	0402
R452	1430770	Chip resistor	4.7 k	5 % 0.063 W	0402
R453	1430700	Chip resistor	10	5 % 0.063 W	0402
R454	1430724	Chip resistor	82	5 % 0.063 W	0402
R455	1430690	Chip jumper		0402	
R520	1430774	Chip resistor	6.8 k	5 % 0.063 W	0402
R521	1430784	Chip resistor	15 k	5 % 0.063 W	0402
R522	1430770	Chip resistor	4.7 k	5 % 0.063 W	0402
R523	1430690	Chip jumper		0402	
R530	1430724	Chip resistor	82	5 % 0.063 W	0402
R531	1430734	Chip resistor	220	5 % 0.063 W	0402
R532	1430700	Chip resistor	10	5 % 0.063 W	0402
R641	1430726	Chip resistor	100	5 % 0.063 W	0402
R642	1430770	Chip resistor	4.7 k	5 % 0.063 W	0402
R643	1430770	Chip resistor	4.7 k	5 % 0.063 W	0402
R644	1430690	Chip jumper		0402	
R645	1430792	Chip resistor	33 k	5 % 0.063 W	0402
R646	1430770	Chip resistor	4.7 k	5 % 0.063 W	0402
R647	1430700	Chip resistor	10	5 % 0.063 W	0402
R648	1430804	Chip resistor	100 k	5 % 0.063 W	0402
R651	1430796	Chip resistor	47 k	5 % 0.063 W	0402
R652	1430786	Chip resistor	18 k	5 % 0.063 W	0402
R653	1430754	Chip resistor	1.0 k	5 % 0.063 W	0402
R654	1430778	Chip resistor	10 k	5 % 0.063 W	0402
R655	1430808	Chip resistor	150 k	5 % 0.063 W	0402

R656	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R658	1430690	Chip jumper	0402	
R659	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R660	1430690	Chip jumper	0402	
R731	1430766	Chip resistor	3.9 k	5 % 0.063 W 0402
R741	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R742	1430762	Chip resistor	2.2 k	5 % 0.063 W 0402
R743	1430796	Chip resistor	47 k	5 % 0.063 W 0402
R745	1430762	Chip resistor	2.2 k	5 % 0.063 W 0402
R746	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R747	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R752	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R753	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R754	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R755	1430710	Chip resistor	22	5 % 0.063 W 0402
R760	1430812	Chip resistor	220 k	5 % 0.063 W 0402
R767	1430764	Chip resistor	3.3 k	5 % 0.063 W 0402
R768	1430794	Chip resistor	39 k	5 % 0.063 W 0402
R769	1430796	Chip resistor	47 k	5 % 0.063 W 0402
R770	1430788	Chip resistor	22 k	5 % 0.063 W 0402
R771	1430776	Chip resistor	8.2 k	5 % 0.063 W 0402
R775	1430690	Chip jumper	0402	
R777	1430690	Chip jumper	0402	
R790	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R791	1430788	Chip resistor	22 k	5 % 0.063 W 0402
R792	1430700	Chip resistor	10	5 % 0.063 W 0402
R793	1430700	Chip resistor	10	5 % 0.063 W 0402
R794	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R795	1430726	Chip resistor	100	5 % 0.063 W 0402
R796	1430796	Chip resistor	47 k	5 % 0.063 W 0402
R797	1430812	Chip resistor	220 k	5 % 0.063 W 0402
R811	1430754	Chip resistor	1.0 k	5 % 0.063 W 0402
R812	1430754	Chip resistor	1.0 k	5 % 0.063 W 0402
R816	1430700	Chip resistor	10	5 % 0.063 W 0402
R820	1430792	Chip resistor	33 k	5 % 0.063 W 0402
R821	1430690	Chip jumper	0402	
R822	1430690	Chip jumper	0402	
R826	1430788	Chip resistor	22 k	5 % 0.063 W 0402
R829	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R830	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R831	1430778	Chip resistor	10 k	5 % 0.063 W 0402
C100	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C101	2604127	Tantalum cap.	1.0 u	20 % 35 V
3.5x2.8x1.9				
C102	2604209	Tantalum cap.	1.0 u	20 % 16 V
3.2x1.6x1.6				
C103	2611668	Tantalum cap.	4.7 u	20 % 10 V

3.2x1.6x1.6					
C104	2604209	Tantalum cap.	1.0 u	20 %	16 V
3.2x1.6x1.6					
C105	2604209	Tantalum cap.	1.0 u	20 %	16 V
3.2x1.6x1.6					
C106	2604209	Tantalum cap.	1.0 u	20 %	16 V
3.2x1.6x1.6					
C107	2604209	Tantalum cap.	1.0 u	20 %	16 V
3.2x1.6x1.6					
C108	2604209	Tantalum cap.	1.0 u	20 %	16 V
3.2x1.6x1.6					
C111	2320530	Ceramic cap.	5.6 p	0.25 %	50 V 0402
C112	2320584	Ceramic cap.	1.0 n	5 %	50 V 0402
C113	2320584	Ceramic cap.	1.0 n	5 %	50 V 0402
C114	2320584	Ceramic cap.	1.0 n	5 %	50 V 0402
C115	2320584	Ceramic cap.	1.0 n	5 %	50 V 0402
C116	2320584	Ceramic cap.	1.0 n	5 %	50 V 0402
C117	2320584	Ceramic cap.	1.0 n	5 %	50 V 0402
C118	2320584	Ceramic cap.	1.0 n	5 %	50 V 0402
C119	2320546	Ceramic cap.	27 p	5 %	50 V 0402
C120	2320584	Ceramic cap.	1.0 n	5 %	50 V 0402
C121	2320584	Ceramic cap.	1.0 n	5 %	50 V 0402
C122	2320584	Ceramic cap.	1.0 n	5 %	50 V 0402
C123	2320620	Ceramic cap.	10 n	5 %	16 V 0402
C124	2320131	Ceramic cap.	33 n	10 %	16 V 0603
C125	2604209	Tantalum cap.	1.0 u	20 %	16 V
3.2x1.6x1.6					
C126	2320083	Ceramic cap.	1.0 n	5 %	50 V 0603
C127	2320560	Ceramic cap.	100 p	5 %	50 V 0402
C128	2320107	Ceramic cap.	10 n	5 %	50 V 0603
C129	2320546	Ceramic cap.	27 p	5 %	50 V 0402
C130	2320546	Ceramic cap.	27 p	5 %	50 V 0402
C131	2320546	Ceramic cap.	27 p	5 %	50 V 0402
C132	2320546	Ceramic cap.	27 p	5 %	50 V 0402
C133	2320620	Ceramic cap.	10 n	5 %	16 V 0402
C140	2320131	Ceramic cap.	33 n	10 %	16 V 0603
C141	2320131	Ceramic cap.	33 n	10 %	16 V 0603
C161	2320546	Ceramic cap.	27 p	5 %	50 V 0402
C201	2307816	Ceramic cap.	47 n	20 %	25 V 0805
C202	2307816	Ceramic cap.	47 n	20 %	25 V 0805
C203	2307816	Ceramic cap.	47 n	20 %	25 V 0805
C210	2320781	Ceramic cap.	47 n	20 %	16 V 0603
C228	2320620	Ceramic cap.	10 n	5 %	16 V 0402
C229	2320620	Ceramic cap.	10 n	5 %	16 V 0402
C231	2320779	Ceramic cap.	100 n	10 %	16 V 0603
C232	2320620	Ceramic cap.	10 n	5 %	16 V 0402
C251	2307816	Ceramic cap.	47 n	20 %	25 V 0805

C260	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C261	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C262	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C263	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C264	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C265	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C266	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C267	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C268	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C269	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C270	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C271	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C272	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C273	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C274	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C275	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C276	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C277	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C278	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C279	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C280	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C281	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C320	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C321	2320532	Ceramic cap.	6.8 p	0.25 % 50 V 0402
C322	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C324	2320538	Ceramic cap.	12 p	5 % 50 V 0402
C325	2320534	Ceramic cap.	8.2 p	0.25 % 50 V 0402
C328	2611668	Tantalum cap.	4.7 u	20 % 10 V
3.2x1.6x1.6				
C331	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C340	2320520	Ceramic cap.	2.2 p	0.25 % 50 V 0402
C341	2320538	Ceramic cap.	12 p	5 % 50 V 0402
C342	2320526	Ceramic cap.	3.9 p	0.25 % 50 V 0402
C343	2320526	Ceramic cap.	3.9 p	0.25 % 50 V 0402
C344	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C345	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C350	2320544	Ceramic cap.	22 p	5 % 50 V 0402
C354	2320530	Ceramic cap.	5.6 p	0.25 % 50 V 0402
C360	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C361	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C362	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C370	2320584	Ceramic cap.	1.0 n	5 % 50 V 0402
C371	2320584	Ceramic cap.	1.0 n	5 % 50 V 0402
C372	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C373	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C374	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C375	2604329	Tantalum cap.	4.7 u	20 % 10 V

3.5x2.8x1.9

C376	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C377	2310490	Ceramic cap.	360 p	2 % 50 V 0805
C378	2320556	Ceramic cap.	68 p	5 % 50 V 0402
C379	2320584	Ceramic cap.	1.0 n	5 % 50 V 0402
C380	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C381	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C382	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C420	2320120	Ceramic cap.	22 n	10 % 25 V 0603
C421	2604209	Tantalum cap.	1.0 u	20 % 16 V

3.2x1.6x1.6

C424	2320618	Ceramic cap.	4.7 n	5 % 25 V 0402
C430	2611668	Tantalum cap.	4.7 u	20 % 10 V

3.2x1.6x1.6

C431	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C432	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C440	2320548	Ceramic cap.	33 p	5 % 50 V 0402
C442	2320548	Ceramic cap.	33 p	5 % 50 V 0402
C443	2320530	Ceramic cap.	5.6 p	0.25 % 50 V 0402
C444	2320520	Ceramic cap.	2.2 p	0.25 % 50 V 0402
C447	2320602	Ceramic cap.	4.7 p	0.25 % 50 V 0402
C448	2320548	Ceramic cap.	33 p	5 % 50 V 0402
C449	2320602	Ceramic cap.	4.7 p	0.25 % 50 V 0402
C450	2320514	Ceramic cap.	1.2 p	0.25 % 50 V 0402
C451	2320514	Ceramic cap.	1.2 p	0.25 % 50 V 0402
C452	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C453	2320548	Ceramic cap.	33 p	5 % 50 V 0402
C454	2320532	Ceramic cap.	6.8 p	0.25 % 50 V 0402
C455	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C520	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C522	2310784	Ceramic cap.	100 n	10 % 25 V 0805
C523	2320781	Ceramic cap.	47 n	20 % 16 V 0603
C524	2320594	Ceramic cap.	2.7 n	5 % 50 V 0402
C525	2320618	Ceramic cap.	4.7 n	5 % 25 V 0402
C530	2611668	Tantalum cap.	4.7 u	20 % 10 V

3.2x1.6x1.6

C531	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C532	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C601	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C602	2320548	Ceramic cap.	33 p	5 % 50 V 0402
C603	2320548	Ceramic cap.	33 p	5 % 50 V 0402
C604	2320602	Ceramic cap.	4.7 p	0.25 % 50 V 0402
C605	2604209	Tantalum cap.	1.0 u	20 % 16 V

3.2x1.6x1.6

C606	2320584	Ceramic cap.	1.0 n	5 % 50 V 0402
C625	2604209	Tantalum cap.	1.0 u	20 % 16 V

3.2x1.6x1.6

C631	2320532	Ceramic cap.	6.8 p	0.25 % 50 V 0402
C633	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C634	2320548	Ceramic cap.	33 p	5 % 50 V 0402
C635	2320530	Ceramic cap.	5.6 p	0.25 % 50 V 0402
C641	2320532	Ceramic cap.	6.8 p	0.25 % 50 V 0402
C642	2320538	Ceramic cap.	12 p	5 % 50 V 0402
C643	2320548	Ceramic cap.	33 p	5 % 50 V 0402
C644	2320548	Ceramic cap.	33 p	5 % 50 V 0402
C645	2320548	Ceramic cap.	33 p	5 % 50 V 0402
C646	2320598	Ceramic cap.	3.9 n	5 % 50 V 0402
C648	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C650	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C652	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C660	2320602	Ceramic cap.	4.7 p	0.25 % 50 V 0402
C701	2320584	Ceramic cap.	1.0 n	5 % 50 V 0402
C703	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C704	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C705	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C706	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C710	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C711	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C712	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C713	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C714	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C715	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C716	2310784	Ceramic cap.	100 n	10 % 25 V 0805
C717	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C721	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C731	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C732	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C733	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C740	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C741	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C742	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C753	2320584	Ceramic cap.	1.0 n	5 % 50 V 0402
C760	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C762	2320779	Ceramic cap.	100 n	10 % 16 V 0603
C763	2604209	Tantalum cap.	1.0 u	20 % 16 V
3.2x1.6x1.6				
C766	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C767	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C770	2320594	Ceramic cap.	2.7 n	5 % 50 V 0402
C771	2320764	Ceramic cap.	6.8 n	10 % 25 V 0402
C772	2320109	Ceramic cap.	15 n	5 % 25 V 0603
C781	2320779	Ceramic cap.	100 n	10 % 16 V 0603
C790	2320779	Ceramic cap.	100 n	10 % 16 V 0603
C791	2320131	Ceramic cap.	33 n	10 % 16 V 0603

C792	2312296	Ceramic cap.		Y5 V 1210
C793	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C794	2320779	Ceramic cap.	100 n	10 % 16 V 0603
C812	2604209	Tantalum cap.	1.0 u	20 % 16 V
3.2x1.6x1.6				
C813	2320534	Ceramic cap.	8.2 p	0.25 % 50 V 0402
C814	2320598	Ceramic cap.	3.9 n	5 % 50 V 0402
C815	2320598	Ceramic cap.	3.9 n	5 % 50 V 0402
C820	2320618	Ceramic cap.	4.7 n	5 % 25 V 0402
C821	2611668	Tantalum cap.	4.7 u	20 % 10 V
3.2x1.6x1.6				
C823	2604209	Tantalum cap.	1.0 u	20 % 16 V
3.2x1.6x1.6				
C824	2320598	Ceramic cap.	3.9 n	5 % 50 V 0402
C825	2604209	Tantalum cap.	1.0 u	20 % 16 V
3.2x1.6x1.6				
C826	2320598	Ceramic cap.	3.9 n	5 % 50 V 0402
L101	3641262	Ferrite bead 30r/100mhz 2a	1206	1206
L102	3641262	Ferrite bead 30r/100mhz 2a	1206	1206
L103	3641262	Ferrite bead 30r/100mhz 2a	1206	1206
L104	3641262	Ferrite bead 30r/100mhz 2a	1206	1206
L320	3645111	Chip coil	3 n	Q=8/100M 0603
L350	3645015	Chip coil	560 n	10 % Q=15/25 MHz
0603				
L360	3608439	Chip coil	820 n	5 % 1206
L361	3608439	Chip coil	820 n	5 % 1206
L370	3640103	Chip coil	320 u	2 % Q=40/796 kHz
1812				
L371	3641302	Chip coil	470 n	5 % Q=30/25 MHz
1008				
L430	3641262	Ferrite bead 30r/100mhz 2a	1206	1206
L631	3641262	Ferrite bead 30r/100mhz 2a	1206	1206
G430	4350115	Vco 872–905mhz 3.0v 10ma tx etacs		ETACS
G520	4350113	Vco 962–995mhz 3.0v 10ma rx etacs		ETACS
G810	4510171	VCTCXO	14.85 M	+–2PPM 3.0V
F101	5119011	SM, fuse f2a 63v	120	1206
F102	5119011	SM, fuse f2a 63v	120	1206
Z100	3640035	Filt z>450r/100m 0r7max 0.2a	0603	0603
Z101	3640035	Filt z>450r/100m 0r7max 0.2a	0603	0603
Z102	3640035	Filt z>450r/100m 0r7max 0.2a	0603	0603
Z103	3640035	Filt z>450r/100m 0r7max 0.2a	0603	0603
Z104	3640035	Filt z>450r/100m 0r7max 0.2a	0603	0603
Z321	4511034	Saw filter	933.5+–16.5 M	5.4x4.7
Z350	4510129	XTAL filter	45 M	+–15KHZ SMD
Z370	4550045	Cer.filt 450+–12.5khz/6db11.8x7.5		
Z660	4512085	Dupl 872–905/917–950mhz	29x14	29x14
V101	1825005	Chip varistor vwm14v vc30v	0805	0805

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V102	1825003	Chip varistor vwm5.5v vc15.5	0805	0805
V103	4113651	Trans. supr.	QUAD	6 V SOT23-5
V120	4100567	Sch. diode x 2	BAS70-04	70V15 mA SER-
SOT23				
V140	4219922	Transistor x 2		UM6
V200	4210102	Transistor	BC858W	pnp 30 V 100 mA
200MWSOT323				
V210	4100567	Sch. diode x 2	BAS70-04	70V15 mA SER-
SOT23				
V320	4210004	Transistor	BFG67X	npn 20 V 50 mA
7.5GHZSOT143				
V340	4115802	Sch. diode x 2	4V	30 mA SOT23
V341	4210090	Transistor	BFG540/X	npn 15 V 129 mA
SOT143				
V380	4210066	Transistor BFR93AWnpn	12 V 35 mA	SOT323
V430	4210066	Transistor BFR93AWnpn	12 V 35 mA	SOT323
V440	4210090	Transistor BFG540/Xnpn	15 V 129 mA	SOT143
V640	4110014	Sch. diode x 2	BAS70-07	70 V 15 mA SOT143
V641	4219922	Transistor x 2		UM6
V650	4219904	Transistor x 2	UMX1	npn 40 V SOT363
V651	4210102	Transistor BC858Wpnp	30 V 100 mA 200MW	SOT323
V740	4210100	Transistor BC848W	npn 30 V	SOT323
V741	4100567	Sch. diode x 2	BAS70-04	70V15 mA
V790	4219922	Transistor x 2		UM6
D002	4340251	IC, EEPROM	NMP40251	SO8S
D700	4340387	IC, 2xbilateral switch	sso TC7W66FU	SSOP8
N100	4370165	Chaps charger control	so16	SO16
N101	4370471	Power asic for etacs/nmt450		
N140	4340059	IC, lp opamp+3/15v r&r	ssolMC7101	SSOP5
N370	4349694	IC, if amp+fm detector	sso TA31136	SSO16
N601	4370099	Rf9102 pw amp	824–849mhz	SO16SQB
N701	4370469	Nasta 4.5 mas	1020a	
N761	4340331	IC, Power amp.	LM4862	P W SO8S
N820	4340393	IC, 2xsynth 1.1ghz	ssopUMA1015AM	SSOP20
X099	5460021	SM, conn	2x14m spring p1.0	pcb/p PCB/PCB
X101	5469069	SM, batt conn	2pol spr p3.5	100v 100V2A
X102	5469069	SM, batt conn	2pol spr p3.5	100v 100V2A
X103	5469061	SM, system conn	6af+3dc+mic+jack	
A300	9517011	Shield assembly-4	dmc00508	
A400	9517010	Shield assembly-3	dmc00507	
A500	9517010	Shield assembly-3	dmc00507	
A600	9517011	Shield assembly-4	dmc00508	
	9510480	Antenna clip	dmd04121	nhx-7
	9854322	PCB JP3	41.0X111.95X1.0	M4 4/PA
	0240775	SW program	MCU	for NHX-7

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